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OFFICE OF PETITIONS

EXHIBIT A

U.S. SERIAL NO.: 10/521,619

ASSIGNMENT OF PATENTS

This Assignment of Patents (this "Assignment") is effective as of the Initial Closing Date (as defined in the Asset Purchase Agreement (the "Asset Purchase Agreement"), dated as of October 10, 2003, by and among ASML Holding N.V., a Dutch company ("Parent"), ASML U.S., Inc., a Delaware corporation and a wholly-owned subsidiary of Parent ("Seller U.S."), and the other affiliates of Seller U.S. party thereto (together with all of the foregoing parties, each a "Seller" and collectively the "Sellers"), on the one hand, and Thermal Acquisition Corp., a Delaware corporation ("Buyer"). Capitalized terms used herein but not defined shall have the meanings ascribed to such terms in the Asset Purchase Agreement.

WHEREAS, upon the terms and subject to the conditions in the Asset Purchase Agreement, Sellers have agreed to assign and transfer to Buyer, among other things, certain Patents (as defined below);

WHEREAS, in order to further effect the assignment and transfer of such Patents, Buyer has requested that Seller U.S. execute and deliver to Buyer this Assignment;

NOW, THEREFORE, for good and valuable consideration, the receipt and sufficiency of which is hereby acknowledged:

1. Sellers agree to and hereby do assign, sell, transfer, grant and convey to Buyer, its successors and assigns, all of Sellers' worldwide right, title and interest in and to all Patents listed on schedule 3.18(a)(i) of the Disclosure Schedule and all causes of action, demands, judgments, claims, or other similar rights of Sellers relating primarily to such Patents.

"Patents" shall mean all U.S. and foreign patents and applications therefor and all reissues, divisions, renewals, extensions, provisionals, continuations and continuations-in-part thereof.

2. Sellers authorize and request the United States Patent and Trademark Office and head of any foreign patent office to issue all patent registrations which may issue on any applications for any Patents to Buyer, its successors and assigns, in accordance with this Assignment.

3. Promptly upon the request of Buyer, Sellers shall execute such documents and perform such actions as may be necessary to perfect the assignment of rights contained in this Assignment.

4. Nothing herein shall affect, or be deemed to affect, the representations, warranties, covenants, and indemnities contained in the Asset Purchase Agreement.

5. This Assignment may be executed in one or more counterparts and signature may be delivered by facsimile, each of which shall be deemed an original, but all of which together shall constitute one and the same instrument.

ASML U.S., Inc.

By:

C. Douglas Marsh

**Title: Vice President Business Integration
& U.S. Institutional Relations**

Thermal Acquisition Corp., a Delaware Corporation

By:

Title: President and Chief Executive Officer

IN WITNESS WHEREOF, Seller U.S. has caused this instrument to be executed by its duly authorized corporate officer as of the Closing Date.

ASML U.S., Inc.

By: _____

Name: C. Douglas Marsh
Title: Vice President Business Integration
& U.S. Institutional Relations

ACKNOWLEDGED AND AGREED:

Thermal Acquisition Corp., a Delaware Corporation

By: _____

Name: Jerauld Cutini
Title: President and Chief Executive Officer

DISCLOSURE SCHEDULES

SCHEDULE 3.18(a)(I)

The following Patents:

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Attachment 1 to

Disclosure Schedule 3.18(a)(i)

Reference No.		Title/Inventors	Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
A	16178	6	AJT	LOW TEMPERATURE CHEMICAL VAPOR DEPOSITION OF SILICON DIOXIDE FILMS	
FA	16178	6-JP	AJT	07/068,727 06/29/87	
A	16178	7	AJT	LOW TEMPERATURE CHEMICAL VAPOR DEPOSITION OF SILICON DIOXIDE FILMS	Japan
FA	16178	7-JP	AJT	61-137340 06/14/86	
A	16178	8	AJT	CVD REACTOR AND GAS INJECTION SYSTEM	
FA	16178	8	AJT	07/044,326 10/27/87	
A	16178	8	AJT	CVD REACTOR AND GAS INJECTION SYSTEM	Japan
A	40356		AJT	61-165449 07/14/86	
A	44048		AJT	FLUIDIZED BED HEATER FOR SEMICONDUCTOR PROCESSING	
FA	44048	JP	AJT	707262 03/01/85	
FA	44048	KR	AJT	06/16/87	
A	44153		AJT	RAPID INFRARED CURING OF PHENOL PHENOLIC, EPOXY AND OTHER RESINS/Alley, Kurita, et al	
A	44521		AJT	ATMOSPHERIC PRESSURE CHEMICAL VAPOR DEPOSITION APPARATUS AND METHOD/ Bartholomew	
A	44521	1	AJT	07/128,806 12/04/87	
FA	44521	1	AJT	ATMOSPHERIC PRESSURE CHEMICAL VAPOR DEPOSITION APPARATUS AND METHOD/ Bartholomew	Japan
FA	44521	1	AJT	63-307653 12/05/88	
FA	44521	1	AJT	2930960 05/21/99	
FA	44521	1	AJT	ATMOSPHERIC PRESSURE CHEMICAL VAPOR DEPOSITION APPARATUS AND METHOD/ Bartholomew	South Korea
FA	44521	1	AJT	Closed	
FA	44521	1	AJT	INDUSTRIAL ROBOT FOR USE IN CLEAN ROOM/ Stevens	
FA	44521	1	AJT	07/089,591 08/26/87	Expired
FA	44521	1	AJT	METHOD FOR IMPROVING STEP COVERAGE OF DIELECTRIC IN VLSI CIRCUITS/Shamsholun	Abandoned
FA	44521	1	AJT	06/907,503 09/15/86	Abandoned
FA	44521	1	AJT	METHOD FOR IMPROVING THE STEP COVERAGE OF DIELECTRIC IN VLSI CIRCUITS/Shamsholun	
FA	44521	1	AJT	07/214,909 06/29/88	
FA	44521	1	AJT	4,891,247 01/02/90	Abandoned

I-71935/MSS (461055-828)

1059128

Reference No.			Title/Inventors		Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
FA	44521	1-JP	AJT	BOROSILICATE GLASS FILMS FOR MULTILEVEL METALLIZATION STRUCTURES IN SEMICONDUCTOR DEVICES AND METHOD	62-231991 09/16/87	Abandoned	Japan
FE	44521	1-EP	AJT	METHOD FOR IMPROVING THE STEP COVERAGE OF DIELECTRIC IN VLSI CIRCUITS	Closed		Europe
A	47444		AJT. MSS	CHEMICAL VAPOR DEPOSITION USING DYED SILANE/Gralenski	07/238,826 08/31/88	Abandoned in favor of 07/798,829 (A-47444-1)	
FA	47444	DE	AJT. MSS	CHEMICAL VAPOR DEPOSITION USING DISILANE/Gralenski	P3928765.3 08/30/89	Abandoned	Germany
FA	47444	KR	AJT MSS	CHEMICAL VAPOR DEPOSITION USING DISILANE/Gralenski	1247289 08/31/89	Abandoned	South Korea
FA	47444	JP	AJT MSS	CHEMICAL VAPOR DEPOSITION USING DISILANE/Gralenski	01-226366 08/31/89	Abandoned	Japan
FA	47444	GB	AJT. MSS	PROCESSES USING DISILANE/Gralenski	8919291.8 08/24/89	2222416/ 03/03/93 Abandoned	United Kingdom
FE	47444	EP	AJT MSS	CHEMICAL VAPOR DEPOSITION USING DYED SILANE/Gralenski	Closed		Europe
FP	47444	PC	AJT MSS	CHEMICAL VAPOR DEPOSITION USING DYED SILANE/Gralenski	Closed		PCT
A	47444	1	AJT MSS	CHEMICAL VAPOR DEPOSITION USING DISILANE/Gralenski	07/798,829 11/22/91	Abandoned in favor of 07/991,500 (A-47444-2)	
A	47444	2	AJT MSS	CHEMICAL VAPOR DEPOSITION USING DISILANE/Gralenski	07/991,500 12/17/92	Abandoned in favor of 08/329,772 (A-47444-3)	
A	47444	3	AJT MSS	CHEMICAL VAPOR DEPOSITION USING DISILANE/Gralenski	08/329,772 10/27/94	Abandoned per client ltr 09/14/98	
A	52244		AJT.	ELECTRICALLY INSULATED PIPE COUPLING APPARATUS/Gralenski	07/570,122 08/17/90	5,088,773 02/18/92	
A	52353		AJT WSG	INJECTOR AND METHOD FOR DELIVERING GASEOUS CHEMICALS TO A SURFACE/Bartholomew	07/542,243 06/21/90	5,136,975 08/11/92	
A	52354		AJT	SELF CLEANING ORIFICE/Kamian	07/513,807	5,113,789	

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Reference No.			Title/Inventors		Serial No/ Filing Date	Patent No/ Issue Date	Foreign Countries
FA	52354	KR	WSG	SELF CLEANING FLOW CONTROL ORIFICE/Kamian	04/24/90	05/19/92	
FA	52354	JP	AJT WSG	SELF CLEANING FLOW CONTROL ORIFICE/Kamian	14/08/90 09/18/90	188614 01/13/99	South Korea
FA	52354	TW	AJT WSG	SELF CLEANING FLOW CONTROL ORIFICE/Kamian	2-216935 08/17/90	2973490 09/03/99	Japan
FE	52354	DE	AJT WSG	SELF CLEANING FLOW CONTROL ORIFICE/Kamian	79106834 08/15/90	51810 02/14/92	Taiwan
FE	52354	ES	AJT WSG	SELF CLEANING FLOW CONTROL ORIFICE/Kamian	90307398.9 07/06/90	69017008 02/15/95	Germany
FE	52354	FR	AJT WSG	SELF CLEANING FLOW CONTROL ORIFICE/Kamian	90307398.9 07/06/90	453679 02/15/95 Abandoned	Spain
FE	52354	GB	AJT WSG	SELF CLEANING FLOW CONTROL ORIFICE/Kamian	90307398.9 07/06/90	453679 02/15/95	France
FE	52354	GR	AJT WSG	SELF CLEANING FLOW CONTROL ORIFICE/Kamian	90307398.9 07/06/90	453679 02/15/95	United Kingdom
FE	52354	IT	AJT WSG	SELF CLEANING FLOW CONTROL ORIFICE/Kamian	90307398.9 07/06/90	453679 02/15/95 Abandoned	Greece
FE	52354	BE	AJT	SELF CLEANING FLOW CONTROL ORIFICE/Kamian	90307398.9 07/06/90	453679 02/15/95	Italy
FE	52354	CH	AJT WSG	SELF CLEANING FLOW CONTROL ORIFICE/Kamian	90307398.9 07/06/90	453679 02/15/95 Abandoned	Belgium
FE	52354	EP	AJT WSG	SELF CLEANING FLOW CONTROL ORIFICE/Kamian	90307398.9 07/06/90	453679 02/15/95 Abandoned	Switzerland
FE	52354	LU	AJT WSG	SELF CLEANING FLOW CONTROL ORIFICE/Kamian	90307398.9 07/06/90	453679 02/15/95	Europe
FE	52354	NL	AJT WSG	SELF CLEANING FLOW CONTROL ORIFICE/Kamian	90307398.9 07/06/90	453679 02/15/95 Abandoned	Luxembourg
FE	52354	SE	AJT WSG	SELF CLEANING FLOW CONTROL ORIFICE/Kamian	90307398.9 07/06/90	453679 02/15/95	Netherlands
FE	52354		AJT WSG	SELF CLEANING FLOW CONTROL ORIFICE/Kamian	90307398.9 07/06/90	453679 02/15/95	Sweden

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Reference No.			Title/Inventors		Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
FE	52354	DK	AJT WSG	SELF CLEANING FLOW CONTROL ORIFICE/Kamian	90307398.9 07/06/90	Abandoned 453679 02/15/95 Abandoned	Denmark
FE	52354	AT	AJT	SELF CLEANING FLOW CONTROL ORIFICE/Kamian	90307398.9 07/06/90	453679 02/15/95 Abandoned	Austria
A	53835		AJT JEM	U-SHAPED HEATER LINES/Walker	07/601,261 10/22/90	Abandoned 08/19/92	
FA	53835	KR	AJT	U-SHAPED HEATER LINES/Walker	18591/91 10/22/91	Abandoned 08/19/92	South Korea
FA	53835	JP	AJT	U-SHAPED HEATER LINES/Walker	3-274072 10/22/91	Abandoned 08/19/92	Japan
FE	53835	EP	AJT	HEATED FLUID SUPPLY LINE/Walker	91309735.8 10/22/91	Abandoned	Europe
A	53836		AJT	LIQUID SOURCE BUBBLER/Richie	07/601,270 10/22/90	5,078,922 01/07/92	
FA	53836	JP	AJT	LIQUID SOURCE BUBBLER/Richie	3-274069 10/22/91	1929857 05/12/95	Japan
FA	53836	KR	AJT MSS	LIQUID SOURCE BUBBLER/Richie	18592/91 10/22/91	191851 01/27/99	South Korea
FE	53836	EP	AJT	LIQUID SOURCE BUBBLER/Richie	91309736.6 10/22/91	Abandoned	Europe
A	53837		AJT	X-RAY TUBE INCLUDING FLUID X-RAY SOURCE/Gmolencki	Closed		
A	53859		AJT	LIQUID LEVEL SENSOR ASSEMBLY/Goodrich	07/601,408 10/23/90	5,029,471 07/09/91	
FA	53859	JP	AJT	LIQUID LEVEL SENSOR ASSEMBLY/Goodrich	3-275317 10/23/91	1903072 02/08/95	Japan
FA	53859	KR	AJT MSS	LIQUID LEVEL SENSOR ASSEMBLY/Goodrich	18633-91 10/23/91	216658 06/01/99	South Korea
FE	53859	EP	AJT	LIQUID LEVEL SENSOR ASSEMBLY/Goodrich	91309743.2 10/22/91	Abandoned	Europe

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Reference No.		Title/Inventors		Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
A	53860		AJT	VAPOR DELIVERY SYSTEM	Closed	
A	53861		AJT	CHEMICAL REFILL SYSTEM	Closed	
A	56598		AJT	HEATER FOR PROCESSING GASES/Collins	07/971,490 11/04/92	
FA	56598	JP	AJT	GAS HEATER FOR PROCESSING GASES/Collins	6-511396 11/03/93	Japan
FA	56598	KR	AJT	GAS HEATER FOR PROCESSING GASES/Collins	701790/95 11/03/93	South Korea
FE	56598	EP	AJT	GAS HEATER FOR PROCESSING GASES/Collins	94900500.3 11/03/93	Europe
FE	56598	HK	AJT	GAS HEATER FOR PROCESSING GASES/Collins	98114622.0 12/22/98	Hong Kong
FE	56598	DE	AJT	GAS HEATER FOR PROCESSING GASES/Collins	94900500.3 11/03/93	Germany
FE	56598	FR	AJT	GAS HEATER FOR PROCESSING GASES/Collins	94900500.3 11/03/93	France
FE	56598	GB	AJT	GAS HEATER FOR PROCESSING GASES/Collins	94900500.3 11/03/93	Great Britain
FE	56598	IT	AJT	GAS HEATER FOR PROCESSING GASES/Collins	94900500.3 11/03/93	Italy
EP	56598	PC	AJT	GAS HEATER FOR PROCESSING GASES/Collins	PCT/US93/10532 11/03/93	PCT
A	57727		AJT	BPSG STABILITY ENHANCING CAP LAYER/ Engdahl	Closed	
A	57728		AJT	OZONE PRETREATMENT FOR IMPROVED VIA RESISTANCE/Curtis	Closed	
A	58019		AJT	CHEMICAL VAPOR DEPOSITION OF SILICON DIOXIDE USING HEXAMETHYLDISILAZANE/Krusell	08/071,516 06/03/93	
EP	58019	PC	AJT	CHEMICAL VAPOR DEPOSITION OF SILICON DIOXIDE FROM HEXAMETHYLDISILAZANE AND OZONE/OXYGEN/Krusell	5,304,398 04/19/94	PCT

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Reference No.			Title/Inventors		Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
A	59071		AJT	A THIN FILM SEMICONDUCTOR DEVICE AND METHOD/Harada	08/191,091 02/03/94	Abandoned	
FP	59071	PC	AJT	A THIN FILM SEMICONDUCTOR DEVICE AND METHOD/Harada	PCT/US94/01352 02/04/94	Abandoned	PCT
A	59072		AJT	METHOD OF MANUFACTURING A GLASS SUBSTRATE FOR A THIN FILM/Harada	08/191,093 02/03/94	Abandoned in favor of FWC 08/542,279 (A-59072-1)	
FP	59072	PC	AJT	METHOD OF MANUFACTURING A GLASS SUBSTRATE FOR A THIN FILM/Harada	PCT/US94/01278 02/04/94	Abandoned	PCT
A	59072	1	AJT MSS	METHOD OF MANUFACTURING A GLASS SUBSTRATE FOR A THIN FILM/Harada	08/542,279 10/12/93	Abandoned	
A	59073		AJT MSS	METHOD OF MANUFACTURING SIDE WALLS AND SEMICONDUCTOR DEVICE HAVING SIDE WALLS/ Harada, Hattori	08/237,691 05/04/94	Abandoned in favor of FWC 08/512,346 (A-59073-1)	
FP	59073	PC	AJT MSS	METHOD OF MANUFACTURING SIDE WALLS AND SEMICONDUCTOR WITH SIDE WALLS/Harada, Hattori	PCT/US94/05315 03/13/94	Abandoned	PCT
A	59073	1	AJT MSS	METHOD OF MANUFACTURING SIDE WALLS AND SEMICONDUCTOR DEVICE HAVING SIDE WALLS/ Harada, Hattori	08/512,346/ 08/08/95 FWC of 08/237,691 Filed 05/04/94	Abandon	
A	59425		AJT	TRIETHOXYLANE (TRIS) AS A PRECURSOR FOR THE DEPOSITION OF SiO ₂ /Schmidt	Closed		
A	59471		AJT MSS	SINGLE BODY INJECTOR AND METHOD FOR DELIVERING GASES TO A SURFACE/Dedmonney	08/276,815 07/18/94	Abandoned in favor of FWC 08/621,772 (A-59471-1)	
FA	59471	JP	AJT MSS	SINGLE BODY INJECTOR FOR DELIVERING GASES TO A SURFACE/Dedmonney	7-181702 07/18/95	2790437 06/12/98	Japan
FA	59471	KR	AJT MSS	SINGLE BODY INJECTOR FOR DELIVERING GASES TO A SURFACE/Dedmonney	20958/95 07/18/95	190355 01/20/99	South Korea
FA	59471	TW	AJT MSS	SINGLE BODY INJECTOR FOR DELIVERING GASES TO A SURFACE/Dedmonney	84100288 01/13/95	106107 12/29/99	Taiwan
FE	59471	DE	AJT MSS	SINGLE BODY INJECTOR FOR DELIVERING GASES TO A SURFACE/Dedmonney	95304783.4 07/10/95	P69513104.4 11/03/99	Germany

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Reference No.			Title/Inventors		Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
FE	59471	EP	AJT. MSS	SINGLE BODY INJECTOR FOR DELIVERING GASES TO A SURFACE/Dedmontney	95304783.4 07/10/95	0697376 11/03/99	Europe
FE	59471	FR	AJT. MSS	SINGLE BODY INJECTOR FOR DELIVERING GASES TO A SURFACE/Dedmontney	95304783.4 07/10/95	0697376 11/03/99	France
FE	59471	GB	AJT. MSS	SINGLE BODY INJECTOR FOR DELIVERING GASES TO A SURFACE/Dedmontney	95304783.4 07/10/95	0697376 11/03/99	Great Britain
FE	59471	HK	AJT. MSS	SINGLE BODY INJECTOR	98111870.5 11/09/98	1011010B 06/16/00	Hong Kong
FE	59471	IT	AJT. MSS	SINGLE BODY INJECTOR FOR DELIVERING GASES TO A SURFACE/Dedmontney	95304783.4 07/10/95	Abandoned	
FE	59471	NL	AJT. MSS	SINGLE BODY INJECTOR FOR DELIVERING GASES TO A SURFACE/Dedmontney	95304783.4 07/10/95	0697376 11/03/99	Italy
A	59471	1	AJT. MSS	SINGLE BODY INJECTOR AND METHOD FOR DELIVERING GASES TO A SURFACE/Dedmontney, Gralenski, Miller	95304783.4 07/10/95	0697376 11/03/99	Netherlands
A	59471	2	AJT. MSS	METHOD OF MANUFACTURING AN INJECTOR FOR CHEMICAL VAPOR DEPOSITION PROCESSING/Dedmontney, Gralenski, Miller	08/621,772 03/22/96 FWC of 08/276,815 Filed 07/18/94	5,683,516 11/04/97	
A	59471	3	AJT. MSS	SINGLE BODY INJECTOR FOR DELIVERING GASES TO A SURFACE/Miller, Dobkin	08/892,469 07/14/97 CIP of 08/621,772; which is an FWC of 08/276,815	5,935,647 08/10/99	
FA	59471	3-TW	AJT. MSS	SINGLE BODY INJECTOR FOR DELIVERING GASES TO A SURFACE/Miller, Dobkin	87111447 07/14/98	6,022,414 02/08/00	Taiwan
A	59471	4	AJT. MSS SMF	SINGLE BODY INJECTOR AND DEPOSITION CHAMBER/Miller, Dobkin	09/113,823 07/10/98 CIP of 08/892,469; which is a CIP of 08/621,772; which is an FWC of	6,200,389 03/13/01	

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Reference No.			Title/Inventors		Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
FP	59471	4-PC AJT MSS	SINGLE BODY INJECTOR AND DEPOSITION CHAMBER/Miller, et al.		08/27/815		
FA	59471	4-CN AJT MSS	SINGLE BODY INJECTOR AND DEPOSITION CHAMBER/Miller, et al.		PCT/US98/14393 07/10/98	Closed	PCT
FA	59471	4-HK AJT MSS	SINGLE BODY INJECTOR AND DEPOSITION CHAMBER/Miller, et al.		98807203.3 07/10/98		China
FA	59471	4-JP AJT MSS	SINGLE BODY INJECTOR AND DEPOSITION CHAMBER/Miller, et al.		00108287.5 12/21/00		
FA	59471	4-KR AJT MSS	SINGLE BODY INJECTOR AND DEPOSITION CHAMBER/Miller, et al.		2000-503260 07/10/98		Japan
FA	59471	4-SG AJT MSS	SINGLE BODY INJECTOR AND DEPOSITION CHAMBER/Miller, et al.		2000-7000430 07/10/98	355058 09/29/02	South Korea
FE	59471	4-EP AJT MSS	SINGLE BODY INJECTOR AND DEPOSITION CHAMBER/Miller, et al.		9906104-6 07/10/98	69697 03/04/02	Singapore
A	59471	5 AJT MSS SMF	SINGLE BODY INJECTOR AND DEPOSITION CHAMBER/Miller, Dobkin		98933329.9 07/10/98		Europe
A	60164		METHOD OF FORMING A PLANAR LAYER OF MATERIAL/Fry, Lightfoot, Lomond		09/757,542 01/09/01	6,521,048 02/18/03	
FA	60164	KR AJT MSS	METHOD OF PLANARIZING A LAYER OF MATERIAL/Fry, Lightfoot, Lomond		08/447,809 05/23/95	5,668,063 09/16/97	
FA	60164	JP AJT MSS	METHOD OF PLANARIZING A LAYER OF MATERIAL/Fry, Lightfoot, Lomond		708269/97 05/06/96		South Korea
FE	60164	EP AJT MSS	METHOD OF PLANARIZING A LAYER OF MATERIAL/Fry, Lightfoot, Lomond		8-535689 05/06/96		Japan
FP	60164	PC AJT MSS	METHOD OF PLANARIZING A LAYER OF MATERIAL/Fry, Lightfoot, Lomond		96914585.3 05/06/96	Abandoned	Europe
A	62201		STRESS RELIEF OF APCVD OXIDE FILMS/Fry		PCT/US96/06375 05/06/96	Closed	PCT
A	62732		NITROGEN SHIELD/Van Tran		08/704,227 08/27/96	5,786,278 07/28/98	
					08/800,106	Abandoned in favor of FWC 08/976,928	

I-71935/MSS (463035-828)
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Reference No.		Title/Inventors		Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
A	62732	1	JEM	02/13/97	(A-62732-1)	
			AJT	08/976,928	5,944,900	
A	62732	2	AJT	11/24/97	08/31/99	
			JEM	Closed		
A	62786		AJT	08/573,318	Abandoned in favor	
			MSS	12/15/95	of 08/599,092	
A	62786	1	AJT	08/599,092	(A-62786-1)	
			MSS	02/07/96	Abandoned	
				CIP of 08/573,318		
				Filed 12/15/95		
FA	62786	1-CN	AJT	96198872.X		China
			MSS	12/11/96		
FA	62786	1-JP	AJT	9-522910		Japan
			MSS	12/11/96		
FA	62786	1-KR	AJT	704363/98		South Korea
			MSS	12/11/96		
FA	62786	1-SG	AJT	9802389-8	51957	Singapore
			MSS	12/11/96	08/22/00	
FA	62786	1-TW	AJT	83109526	088844	Taiwan
			MSS	08/06/96	12/13/97	
FB	62786	1-EP	AJT	96943723.5		Europe
			MSS	12/11/96		
FB	62786	1-HK	AJT	99100518.5	Abandoned	Hong Kong
			MSS	02/08/99		
FP	62786	1-PC	AJT	PCT/US96/19819	Closed	PCT
			MSS	12/11/96		
A	62998		AJT		Closed	
			MSS			
A	63007		AJT		Closed	
			JEM			
A	63008		AJT	08/801,997	5,855,957	

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Reference No.			Title/Inventors		Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
FA	63008	TW	JEM	DEPOSITION	02/18/97	01/05/99	
FP	63008	PC	AJT JEM	OPTIMIZING SiO ₂ FILM CONFORMALITY IN TEOS/03 APCVD	87012245 02/18/98	107673 02/02/00	Taiwan
A	63265		AJT MSS	OPTIMIZATION OF SiO ₂ FILM CONFORMALITY IN ATMOSPHERIC PRESSURE CHEMICAL VAPOR DEPOSITION	PCT/US98/02842 02/17/98	Abandoned	PCT
FP	63265	PC	AJT MSS	LOW K DIELECTRICS PREPARED FROM CROSS-LINKED PPXS (CL-PPXS)/Lee	08/679,864 07/16/96	5,925,420 07/20/99	
A	63347		AJT MSS	CROSSLINKED AROMATIC POLYMERS SA LOW K DIELECTRIC/Lee	PCT/US97/10575 07/14/97	Abandoned	PCT
A	63579		AJT MSS	A METHOD OF PLANARIZING A DIELECTRIC LAYER WITH REDUCED HYDROGEN DIFFUSION/ Eakin	Closed		
A	63660		AJT JEM	LOW K DIELECTRICS PREPARED FROM PECVD AND PECVD OF SELECTED SILOXANES/Lee	Hold		
A	63661		AJT MSS	HIGH TEMPERATURE ROLLER MODULE/Kleiner	09/019,349 02/05/98	5,976,258 11/02/99	
A	63662		AJT	METHOD FOR FORMING VERTICALLY EXTENDED EMBEDDED LOW K MATERIALS/Py	Closed		
A	63665		AJT MSS	OPTIMIZATION OF SiO ₂ FILM CONFORMITY	Closed		
FA	63665	CN	AJT MSS	METHOD OF CONTAMINATION REDUCTION BY FORMATION OF ALL OXIDE SURFACE LAYERS/Bailey, Brady	08/823,655 03/11/97	5,916,378 06/29/99	China
FA	63665	HK	AJT MSS	METHOD OF CONTAMINATION REDUCTION BY FORMATION OF ALL OXIDE SURFACE LAYERS/Bailey, Brady	98804123.5 03/06/98		
FA	63665	JP	AJT MSS	METHOD OF CONTAMINATION REDUCTION BY FORMATION OF ALL OXIDE SURFACE LAYERS/Bailey, Brady	00106069.3 09/26/00	Abandoned	Hong Kong
FA	63665	KR	AJT	METHOD OF CONTAMINATION REDUCTION BY FORMATION OF ALL OXIDE SURFACE LAYERS/Bailey, Brady	10-339667 03/10/98		Japan
FA	63665		AJT	METHOD OF CONTAMINATION REDUCTION BY	99-7008224		South Korea

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Reference No.		Title/Inventors		Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
PA	63665	SG	MSS	FORMATION OF ALL OXIDE SURFACE LAYERS/Bailey, Brady	03/06/98	
PA	63665	TW	AJT MSS	METHOD OF CONTAMINATION REDUCTION BY FORMATION OF ALL OXIDE SURFACE LAYERS/Bailey, Brady	9904062-4 03/06/98	Singapore
FE	63665	EP	AJT MSS	METHOD OF CONTAMINATION REDUCTION BY FORMATION OF ALL OXIDE SURFACE LAYERS/Bailey, Brady	87102978 03/02/98	Taiwan
FP	63665	PC	AJT MSS	METHOD OF CONTAMINATION REDUCTION BY FORMATION OF ALL OXIDE SURFACE LAYERS/Bailey, Brady	98910258.7 03/06/98	Europe
A	63669		AJT MSS	METHOD OF CONTAMINATION REDUCTION BY FORMATION OF ALL OXIDE SURFACE LAYERS/Bailey, Brady	PCT/US98/04570 03/06/98	PCT
FP	63669	PC	AJT MSS	FLANGE CLAMP/Mateos, Kamian	08746,608 11/13/96	Abandoned
A	63672		AJT JEM	FLANGE CLAMP/Mateos, Kamian	PCT/US97/20315 11/06/97	Abandoned PCT
A	63673		AJT JEM MSS	LINEAR INJECTOR WITH VACUUM COMPATIBILITY/Moshagh, Laksell, Herman, Hihl DIRECT DRIVE ROTATIONAL MOTOR WITH AXIAL VACUUM/Moshagh		Closed
A	63674		AJT MSS	INJECTION SEAL/Miller, Veck	08796,300 02/07/97	5,921,560 07/13/99
A	63675		AJT JEM	EXHAUST VENT ASSEMBLY FOR CHEMICAL VAPOR DEPOSITION SYSTEMS/Moshagh		Closed
A	63676		AJT JEM	THERMAL CONDITIONING TOWER/Klainer	08/838,882 04/14/97	5,938,851 08/17/99
A	63677		AJT MSS	MONOBLOK INJECTION MODIFICATION/Moshagh	09/019,342 02/05/98	Abandoned
A	64309		AJT MSS	NITRIC OXIDE COMPOUND CONDENSER/Granados	Closed	
A	64725		AJT	NITROGEN DILUENT GAS FREE OPERATION OF		Combined with A- 59471-3 and closed

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Reference No.			Title/Inventors		Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
			MSS	FLAT PLATE DISCHARGE CHILL OZONE GENERATORS/Granados			
A	64873		AJT MSS	WAFER CARRIER AND SEMICONDUCTOR APPARATUS FOR PROCESSING A SEMICONDUCTOR SUBSTRATE/Yao, Bailey	09/018,021 02/02/98	6,026,589 02/22/00	
A	64873	I	AJT MSS	WAFER CARRIER AND SEMICONDUCTOR APPARATUS FOR PROCESSING A SEMICONDUCTOR SUBSTRATE/Yao, Bailey	09/457,929 12/08/99 Div. of 09/018,021 02/02/98		
FA	64873	CA	AJT MSS	WAFER CARRIER AND SEMICONDUCTOR APPARATUS FOR PROCESSING A SEMICONDUCTOR SUBSTRATE/Yao, Bailey	2319636 02/01/99	Abandoned	Canada
FA	64873	CN	AJT MSS	WAFER CARRIER AND SEMICONDUCTOR APPARATUS FOR PROCESSING A SEMICONDUCTOR SUBSTRATE/Yao, Bailey	99802634.4 02/01/99		China
FA	64873	HK	AJT MSS	WAFER CARRIER AND SEMICONDUCTOR APPARATUS FOR PROCESSING A SEMICONDUCTOR SUBSTRATE/Yao, Bailey	01104936.8 07/16/01	Abandoned	Hong Kong
FA	64873	IL	AJT MSS	WAFER CARRIER AND SEMICONDUCTOR APPARATUS FOR PROCESSING A SEMICONDUCTOR SUBSTRATE/Yao, Bailey	137533 02/01/99	Abandoned	Israel
FA	64873	JP	AJT MSS	WAFER CARRIER AND SEMICONDUCTOR APPARATUS FOR PROCESSING A SEMICONDUCTOR SUBSTRATE/Yao, Bailey	2000-529567 02/01/99		Japan
FA	64873	KR	AJT MSS	WAFER CARRIER AND SEMICONDUCTOR APPARATUS FOR PROCESSING A SEMICONDUCTOR SUBSTRATE/Yao, Bailey	2000-7008430 02/01/99	376643 03/06/03	South Korea
FA	64873	SG	AJT MSS	WAFER CARRIER AND SEMICONDUCTOR APPARATUS FOR PROCESSING A SEMICONDUCTOR SUBSTRATE/Yao, Bailey	200004218-2 02/01/99	74927 08/30/02	Singapore
FA	64873	TW	AJT MSS	WAFER CARRIER/Yao, Bailey	88100719 01/18/99	122455 03/16/01	Taiwan
FE	64873	EP	AJT MSS	WAFER CARRIER AND SEMICONDUCTOR APPARATUS FOR PROCESSING A SEMICONDUCTOR SUBSTRATE/Yao, Bailey	99903586.6 02/01/99		Europe

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Reference No.			Title/Inventors		Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
FP	64873	PC	AJT. MSS	WAFER CARRIER/Yao, Bailey	PCT/US99/02100 02/01/99	Closed	PCT
A	65583		AJT. JEM. MSS	FREE FLOATING SHIELD/DeDennney, et al.	09/008,024 01/16/98	5,849,088 12/15/98	
A	65583	1	AJT. MSS	FREE FLOATING SHIELD AND SEMICONDUCTOR PROCESSING SYSTEM/Bartholomew, et al.	09/185,180 11/03/98 CIP of 09/008,024	6,056,824 05/02/00	
FP	65583	1-PC	AJT. MSS	FREE FLOATING SHIELD AND SEMICONDUCTOR PROCESSING SYSTEM/Bartholomew, et al.	PCT/US98/25740 12/04/98	Closed	PCT
FA	65583	1-CA	AJT. MSS	FREE FLOATING SHIELD AND SEMICONDUCTOR PROCESSING SYSTEM/Bartholomew, et al.	2318147 12/04/98		Canada
FA	65583	1-CN	AJT. MSS	FREE FLOATING SHIELD AND SEMICONDUCTOR PROCESSING SYSTEM/Bartholomew, et al.	98813641.4 12/04/98		China
FA	65583	1-HK	AJT. MSS	FREE FLOATING SHIELD AND SEMICONDUCTOR PROCESSING SYSTEM/Christopher A. Peabody, Jay B. DeDennney, Lawrence D. Bartholomew	01104372.0 06/21/01	Abandoned	Hong Kong
FB	65583	1-EP	AJT. MSS	FREE FLOATING SHIELD AND SEMICONDUCTOR PROCESSING SYSTEM/Bartholomew, et al.	98960728.8 12/14/98		Europe
FA	65583	1-IL	AJT. MSS	FREE FLOATING SHIELD AND SEMICONDUCTOR PROCESSING SYSTEM/Bartholomew, et al.	137315 12/04/98	Abandoned	Israel
FA	65583	1-JP	AJT. MSS	FREE FLOATING SHIELD AND SEMICONDUCTOR PROCESSING SYSTEM/Bartholomew, et al.	2000-540285 12/04/98	3416114 04/04/03	Japan
FA	65583	1-KR	AJT. MSS	FREE FLOATING SHIELD AND SEMICONDUCTOR PROCESSING SYSTEM/Bartholomew, et al.	2000-7007859 12/04/98	345767 07/18/02	South Korea
FA	65583	1-SG	AJT. MSS	FREE FLOATING SHIELD AND SEMICONDUCTOR PROCESSING SYSTEM/Bartholomew, et al.	200003932-1 12/04/98	74790 08/30/02	Singapore
FA	65583	1-TW	AJT. MSS	FREE FLOATING SHIELD AND SEMICONDUCTOR PROCESSING SYSTEM/Bartholomew, et al.	87119658 11/26/98	135711 10/27/01	Taiwan
A	65583	2	AJT. MSS	FREE FLOATING SHIELD AND SEMICONDUCTOR PROCESSING SYSTEM/Bartholomew, et al.	09/492,420 01/27/00 CIP of 09/185,180	6,352,592 B1 03/05/02	
FA	65583	2-CA	AJT. MSS	FREE FLOATING SHIELD AND SEMICONDUCTOR PROCESSING SYSTEM/Bartholomew, et al.	2304548 04/07/00	Abandoned	Canada

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Reference No.				Title/Inventors		Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
FA	65583	2-CN	AJT MSS	FREE FLOATING SHIELD AND SEMICONDUCTOR. PROCESSING SYSTEM/Bartholomew, et al.		00106454.1 04/10/00		China
FE	65583	2-EP	AJT MSS	FREE FLOATING SHIELD AND SEMICONDUCTOR. PROCESSING SYSTEM/Bartholomew, et al.		00302953.5 04/07/00		Europe
FA	65583	2-HK	AJT MSS	FREE FLOATING SHIELD AND SEMICONDUCTOR. PROCESSING SYSTEM/Bartholomew, et al.		0201266.3 02/21/02	Abandoned	Hong Kong
FA	65583	2-JP	AJT MSS	FREE FLOATING SHIELD AND SEMICONDUCTOR. PROCESSING SYSTEM/Bartholomew, et al.		2000-108638 04/10/00		Japan
FA	65583	2-KR	AJT MSS	FREE FLOATING SHIELD AND SEMICONDUCTOR. PROCESSING SYSTEM/Bartholomew, et al.		2000-0018645 04/10/00	338891 05/20/02	South Korea
FA	65583	2-MY	AJT MSS	FREE FLOATING SHIELD AND SEMICONDUCTOR. PROCESSING SYSTEM/Bartholomew, et al.		P20001457 04/07/00		Malaysia
FA	65583	2-SG	AJT MSS	FREE FLOATING SHIELD AND SEMICONDUCTOR. PROCESSING SYSTEM/Bartholomew, et al.		200001878.8 03/31/00		Singapore
FA	65583	2-TW	AJT MSS	FREE FLOATING SHIELD AND SEMICONDUCTOR. PROCESSING SYSTEM/Bartholomew, et al.		89106510 04/08/00		Taiwan
FA	65583	2-TH	AJT MSS	FREE FLOATING SHIELD AND SEMICONDUCTOR. PROCESSING SYSTEM/Bartholomew, et al.		056644 04/03/00	Abandoned	Thailand
A	65816		AJT MSS	CYCLOPHANE DERIVATIVES CONTAINING CROSS-LINKING GROUPS/Golden		Hold.		
A	65965		AJT MSS	LOW K DIELECTRIC INORGANIC/ORGANIC HYBRID FILMS AND METHOD OF MAKING/Rose; Lopata; Felts		09/067,704 04/28/98	6,068,884 05/30/00	
FA	65965	CA	AJT MSS	LOW K DIELECTRIC INORGANIC/ORGANIC HYBRID FILMS AND METHOD OF MAKING/Rose; Lopata; Felts		2,330,040 04/15/99	Abandoned	Canada
FA	65965	CN	AJT MSS	LOW K DIELECTRIC INORGANIC/ORGANIC HYBRID FILMS AND METHOD OF MAKING/Rose; Lopata; Felts		99806506.4 04/15/99		China
FA	65965	HK	AJT MSS	LOW K DIELECTRIC INORGANIC/ORGANIC HYBRID FILMS AND METHOD OF MAKING/Rose; Lopata; Felts		01108034.0 11/15/01	Abandoned	Hong Kong
FA	65965	IL	AJT MSS	LOW K DIELECTRIC INORGANIC/ORGANIC HYBRID FILMS AND METHOD OF MAKING/Rose; Lopata; Felts		139128 04/15/99	Abandoned	Israel

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Reference No.		Title/Inventors		Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
FA	65965	JP	AJT MSS	LOW K DIELECTRIC INORGANIC/ORGANIC HYBRID FILMS AND METHOD OF MAKING/Rose; Lopata; Felts	2000-545704 04/15/99	Japan
FA	65965	KR	AJT MSS	LOW K DIELECTRIC INORGANIC/ORGANIC HYBRID FILMS AND METHOD OF MAKING/Rose; Lopata; Felts	2000-7012019 04/15/99	South Korea
FA	65965	SG	AJT MSS	LOW K DIELECTRIC INORGANIC/ORGANIC HYBRID FILMS AND METHOD OF MAKING/Rose; Lopata; Felts	200005999-8 04/15/99	Singapore
FA	65965	TW	AJT MSS	LOW K DIELECTRIC INORGANIC/ORGANIC HYBRID FILMS AND METHOD OF MAKING/Rose; Lopata; Felts	88106881 04/28/99	Taiwan
FE	65965	EP	AJT MSS	LOW K DIELECTRIC INORGANIC/ORGANIC HYBRID FILMS AND METHOD OF MAKING/Rose; Lopata; Felts	99917529.2 04/15/99	Europe
FP	65965	PC	AJT MSS	LOW K DIELECTRIC INORGANIC/ORGANIC HYBRID FILMS AND METHOD OF MAKING/Rose; Lopata; Felts	PCT/US99/08246 04/15/99	PCT
A	65965	-1	AJT MSS	LOW K DIELECTRIC INORGANIC/ORGANIC HYBRID FILMS AND METHOD OF MAKING/Rose; Lopata; Felts	09/361,667 07/27/99	
A	65965	-2	AJT MSS	LOW K DIELECTRIC INORGANIC/ORGANIC HYBRID FILMS AND METHOD OF MAKING/Rose; Lopata; Felts	10/637,913 08/08/03	
A	66484		AJT MSS	CHEMICAL VAPOR DEPOSITION APPARATUS EMPLOYING LINEAR INJECTORS FOR DELIVERING GASEOUS CHEMICALS AND METHOD/Dobbin; Striffler; McGrogan	Abandoned	
FA	66484	TW	AJT MSS	CHEMICAL VAPOR DEPOSITION APPARATUS EMPLOYING LINEAR INJECTORS FOR DELIVERING GASEOUS CHEMICALS AND METHOD/Dobbin; Striffler; McGrogan	88110478 06/22/99	Taiwan
FP	66484	PC	AJT MSS	CHEMICAL VAPOR DEPOSITION APPARATUS EMPLOYING LINEAR INJECTORS FOR	147614 04/22/02	PCT

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Reference No.		Title/Inventors		Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
P	66959	AJT MSS AJT	DELIVERING GASEOUS CHEMICALS AND METHOD/Dobkin; Stutler; McGrogan WAFER PROCESSING REACTOR HAVING A GAS FLOW CONTROL SYSTEM AND METHOD/ Bartholomew.	60/118,286 02/02/99	Closed	
A	66959	AJT MSS	WAFER PROCESSING REACTOR HAVING A GAS FLOW CONTROL SYSTEM AND METHOD/ Bartholomew; Bailey; Ewald; Boland.	09/493,492 01/28/00	6,143,680 11/07/00	
FA	66959	CA AJT MSS	WAFER PROCESSING REACTOR HAVING A GAS FLOW CONTROL SYSTEM AND METHOD/ Bartholomew; Bailey; Ewald; Boland.	2362694 02/01/00	Abandoned	Canada
FA	66959	CN AJT MSS	WAFER PROCESSING REACTOR HAVING A GAS FLOW CONTROL SYSTEM AND METHOD/ Bartholomew; Bailey; Ewald; Boland.	00804644.1 02/01/00		China
FA	66959	HK MSS	WAFER PROCESSING REACTOR HAVING A GAS FLOW CONTROL SYSTEM AND METHOD/ Bartholomew; Bailey; Ewald; Boland.	021041123 05/31/02	Abandoned	Hong Kong
FA	66959	IL AJT MSS	WAFER PROCESSING REACTOR HAVING A GAS FLOW CONTROL SYSTEM AND METHOD	144696 02/01/00	Abandoned	Israel
FA	66959	JP AJT MSS	WAFER PROCESSING REACTOR HAVING A GAS FLOW CONTROL SYSTEM AND METHOD	2000-599919 02/01/00		Japan
FA	66959	KR AJT MSS	WAFER PROCESSING REACTOR HAVING A GAS FLOW CONTROL SYSTEM AND METHOD	2001-7009763 02/01/00		South Korea
FA	66959	SG AJT MSS	WAFER PROCESSING REACTOR HAVING A GAS FLOW CONTROL SYSTEM AND METHOD	200104725-7 02/01/00		Singapore
FA	66959	TW AJT MSS	WAFER PROCESSING REACTOR HAVING A GAS FLOW CONTROL SYSTEM AND METHOD/ Bartholomew; Bailey; Ewald; Boland	89101846 02/02/00		Taiwan
FB	69959	EP AJT MSS	WAFER PROCESSING REACTOR HAVING A GAS FLOW CONTROL SYSTEM AND METHOD/ Bartholomew; Bailey; Ewald; Boland	00910048.3 02/21/00		Europe
FP	66959	PC AJT MSS	WAFER PROCESSING REACTOR HAVING A GAS FLOW CONTROL SYSTEM AND METHOD/ Bartholomew; Bailey; Ewald; Boland	US00/02606 02/01/00	Closed	PCT

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Reference No.			Title/Inventors		Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
A	66959	1	AJT MSS	WAFER PROCESSING REACTOR HAVING A GAS FLOW CONTROL SYSTEM AND METHOD/ Bertholomew; Bailey; Ewald; Boland;		Closed	
P	67178		AJT MSS	GAS DELIVERY METERING TUBE/Stoddard; Yao; Hamilton; Ingles; DeSa; Kudrjavtsev; Peabody	60/135,358 05/21/99		
A	67178		AJT MSS	GAS DELIVERY METERING TUBE/Ingles; Stoddard; Yao; Hamilton; Young; DeSa	09/470,446 12/22/99		
FA	67178	CA	AJT MSS	GAS DELIVERY METERING TUBE/Ingles; Stoddard; Yao; Hamilton; Young; DeSa	2308758 05/18/00	Abandoned	Canada
FA	67178	CN	AJT MSS	GAS DELIVERY METERING TUBE/Ingles; Stoddard; Yao; Hamilton; Young; DeSa	00108583.2 05/18/00	ZL00108583.2 05/21/03	China
FE	67178	EP	AJT MSS	GAS DELIVERY METERING TUBE/Ingles; Stoddard; Yao; Hamilton; Young; DeSa	00304190.2 05/18/00		Europe
FA	67178	HK	AJT MSS	GAS DELIVERY METERING TUBE/Ingles; Stoddard; Yao; Hamilton; Young; DeSa	01102509.9 04/10/01	Abandoned	Hong Kong
FA	67178	JP	AJT MSS	GAS DELIVERY METERING TUBE/Ingles; Stoddard; Yao; Hamilton; Young; DeSa	2000-148939 05/19/00		Japan
FA	67178	KR	AJT MSS	GAS DELIVERY METERING TUBE/Ingles; Stoddard; Yao; Hamilton; Young; DeSa	2000-0026966 05/19/00		South Korea
FA	67178	MY	AJT MSS	GAS DELIVERY METERING TUBE/Ingles; Stoddard; Yao; Hamilton; Young; DeSa	PI-20002163 05/17/00		Malaysia
FA	67178	SG	AJT MSS	GAS DELIVERY METERING TUBE/Ingles; Stoddard; Yao; Hamilton; Young; DeSa	200002705-2 05/16/00		Singapore
FA	67178	TH	AJT MSS	GAS DELIVERY METERING TUBE/Ingles; Stoddard; Yao; Hamilton; Young; DeSa	057695 05/18/00	Abandoned	Thailand
FA	67178	TW	AJT MSS	GAS DELIVERY METERING TUBE/Ingles; Stoddard; Yao; Hamilton; Young; DeSa	89106456 04/07/00	140755 01/09/02	Taiwan
P	67178	1	MSS MDV	IMPROVED GAS DELIVERY METERING TUBE/DeDombney; DeSa	Unfiled		
A	67178	1	AJT MSS	GAS DELIVERY METERING TUBE/DeDombney; DeSa; Kurita	09/905,349 07/13/01		
FA	67178	1-CN	MSS MDV	GAS DELIVERY METERING TUBE/Anthony Deas; Jay B. DeDombney; Samuel Kurita	02140679.0 07/12/02		China

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Reference No.			Title/Inventors		Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
FA	67178	1-JP	MSS MDV	GAS DELIVERY METERING TUBE/Anthony Desai; Jay B. Dedonney; Samuel Kurita	2002-206050 07/15/02		Japan
FA	67178	1-KR	MSS MDV	GAS DELIVERY METERING TUBE/Anthony Desai; Jay B. Dedonney; Samuel Kurita	2002-0040745 07/12/02		South Korea
FA	67178	1-MY	MSS MDV	GAS DELIVERY METERING TUBE/Anthony Desai; Jay B. Dedonney; Samuel Kurita	07/09/02		Malaysia
FA	67178	1-SG	MSS MDV	GAS DELIVERY METERING TUBE/Anthony Desai; Jay B. Dedonney; Samuel Kurita	200204131-7 07/09/02		Singapore
FA	67178	1-TW	MSS MDV	GAS DELIVERY METERING TUBE/Anthony Desai; Jay B. Dedonney; Samuel Kurita	91115232 07/09/02		Taiwan
FE	67178	1-EP	MSS MDV	GAS DELIVERY METERING TUBE/Desai; DeDonney; Kurita	02254962.0 07/15/02	Abandoned	Europe
A	67388		AJT MSS	METHOD FOR DEPOSITING SILICON DIOXIDE FILM AND PRODUCT/Mahawili	07/370.331 06/22/89	Abandoned	
FA	67388	JP	AJT MSS	METHOD FOR DEPOSITING SILICON DIOXIDE FILM AND PRODUCT/Mahawili	165499/90 06/22/90	2,918,300 04/23/99 Abandoned	Japan
FA	67388	KR	AJT MSS	METHOD FOR DEPOSITING SILICON DIOXIDE FILM AND PRODUCT/Mahawili	1990-9287 06/22/90	162652 09/01/98 Abandoned	South Korea
FA	67388	TW	AJT MSS	METHOD FOR DEPOSITING SILICON DIOXIDE FILM AND PRODUCT/Mahawili	79105124 06/22/90	50934-08/21/91 Abandoned	Taiwan
FE	67388	DE	AJT MSS	METHOD FOR DEPOSITING SILICON DIOXIDE FILM AND PRODUCT/Mahawili	90111648.3 06/20/90	0404101 05/01/96	Germany
FE	67388	EP	AJT MSS	METHOD FOR DEPOSITING SILICON DIOXIDE FILM AND PRODUCT/Mahawili	90111648.3 06/20/90	0404101 05/01/96	Europe
FE	67388	FR	AJT MSS	METHOD FOR DEPOSITING SILICON DIOXIDE FILM AND PRODUCT/Mahawili	90111648.3 06/20/90	0404101 05/01/96	France
FE	67388	GB	AJT MSS	METHOD FOR DEPOSITING SILICON DIOXIDE FILM AND PRODUCT/Mahawili	90111648.3 06/20/90	0404101 05/01/96	Great Britain
FE	67388	NL	AJT MSS	METHOD FOR DEPOSITING SILICON DIOXIDE FILM AND PRODUCT/Mahawili	90111648.3 06/20/90	0404101 05/01/96	Netherlands
A	67388	1	AJT MSS	METHOD FOR DEPOSITING SILICON DIOXIDE FILM AND PRODUCT/Mahawili	07/661.837 02/27/91	Abandoned	

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Reference No.		Title/Inventors		Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
A	67389	AJT MSS	CHEMICAL VAPOR DEPOSITION REACTOR AND METHOD OF OPERATION/Mahawili	07/386,903 07/28/89	4,993,358 02/19/91	
FA	67389	JP MSS	CHEMICAL VAPOR DEPOSITION REACTOR AND METHOD OF OPERATION/Mahawili	201089/90 07/27/90	Abandoned	Japan
FA	67389	KR MSS	CHEMICAL VAPOR DEPOSITION REACTOR AND METHOD OF OPERATION/Mahawili	11454/1990 07/27/90	Abandoned	South Korea
FA	67389	TW MSS	CHEMICAL VAPOR DEPOSITION REACTOR AND METHOD OF OPERATION/Mahawili	79105355 07/29/90	47787 09/26/91 Abandoned	Taiwan
FE	67389	EP MSS	CHEMICAL VAPOR DEPOSITION REACTOR AND METHOD OF OPERATION/Mahawili	90114325.5 07/26/90	Abandoned	Europe
A	67390	AJT MSS	MULTI-ZONE PLANAR HEATER ASSEMBLY AND METHOD OF OPERATION/Mahawili	07/409,125 09/19/89	5,059,770 10/22/91	
FA	67390	JP MSS	MULTI-ZONE PLANAR HEATER ASSEMBLY AND METHOD OF OPERATION/Mahawili	242305/90 09/12/90	2133364 11/14/97	Japan
FA	67390	KR MSS	MULTI-ZONE PLANAR HEATER ASSEMBLY AND METHOD OF OPERATION/Mahawili	14732/90 09/18/90	160510 08/19/98	South Korea
FA	67390	TW MSS	MULTI-ZONE PLANAR HEATER ASSEMBLY AND METHOD OF OPERATION/Mahawili	79105354 07/29/90	51351 01/23/92	Taiwan
FE	67390	EP MSS	MULTI-ZONE PLANAR HEATER ASSEMBLY AND METHOD OF OPERATION/Mahawili	90115336.1 08/10/90	0418541 06/15/94	Europe
FE	67390	DE MSS	MULTI-ZONE PLANAR HEATER ASSEMBLY AND METHOD OF OPERATION/Mahawili	90115336.1 08/10/90	0418541 06/15/94	Germany
FE	67390	FR MSS	MULTI-ZONE PLANAR HEATER ASSEMBLY AND METHOD OF OPERATION/Mahawili	90115336.1 08/10/90	0418541 06/15/94	France
FE	67390	NL MSS	MULTI-ZONE PLANAR HEATER ASSEMBLY AND METHOD OF OPERATION/Mahawili	90115336.1 08/10/90	0418541 06/15/94	Netherlands
FE	67390	GB MSS	MULTI-ZONE PLANAR HEATER ASSEMBLY AND METHOD OF OPERATION/Mahawili	90115336.1 08/10/90	0418541 06/15/94	Great Britain
A	67391	AJT MSS	METHOD OF SOLDERING IN A CONTROLLED-CONVECTION SURFACE-MOUNT REFLOW FURNACE/Alley, Carmasi, Daley, Roffey	07/677,661 03/29/91	5,232,145 08/03/93	
A	67392	AJT MSS	METHOD FOR PRODUCING HIGHLY CONDUCTIVE AND TRANSPARENT FILMS OF TIN AND FLUORIDE DOPED INDIUM OXIDE BY	07/668,858 03/13/91	5,122,391 06/16/92	

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Reference No.		Title/Inventors		Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
FA	67392	JP	AJT. MSS	APCVD/Mayer		
				METHOD FOR PRODUCING HIGHLY CONDUCTIVE AND TRANSPARENT FILMS OF TIN AND FLUORIDE DOPED INDIUM OXIDE BY APCVD/Mayer	Abandoned	Japan
FA	67392	KR	AJT. MSS	APCVD/Mayer		
				METHOD FOR PRODUCING HIGHLY CONDUCTIVE AND TRANSPARENT FILMS OF TIN AND FLUORIDE DOPED INDIUM OXIDE BY APCVD/Mayer	Abandoned	South Korea
FE	67392	EP	AJT. MSS	APCVD/Mayer		
				METHOD FOR PRODUCING HIGHLY CONDUCTIVE AND TRANSPARENT FILMS OF TIN AND FLUORIDE DOPED INDIUM OXIDE BY APCVD/Mayer	Abandoned	Europe
A	67392	1	AJT. MSS	APCVD/Mayer		
				METHOD AND APPARATUS FOR PRODUCING HIGHLY CONDUCTIVE AND TRANSPARENT FILMS OF TIN AND FLUORIDE DOPED INDIUM OXIDE BY APCVD/Mayer	Abandoned	
P	67588		AJT. MSS	PROTECTIVE GAS SHIELD APPARATUS/Stoddard, Yuh	Closed	
A	67588		AJT. MSS	PROTECTIVE GAS SHIELD APPARATUS/Stoddard, Yuh		
FA	67588	CN	AJT. MSS	PROTECTIVE GAS SHIELD APPARATUS/Stoddard, Yuh	6,576,060 04/10/03	
FA	67588	JP	AJT. MSS	PROTECTIVE GAS SHIELD APPARATUS/Neil; Stoddard, Yuh	08807884.X 05/19/00	China
FA	67588	KR	AJT. MSS	PROTECTIVE GAS SHIELD APPARATUS/Neil; Stoddard, Yuh	2000-620151 05/19/00	Japan
FA	67588	SG	AJT. MSS	PROTECTIVE GAS SHIELD APPARATUS/Neil; Stoddard, Yuh	2001-7014850 05/19/00	South Korea
FA	67588	TW	AJT. MSS	PROTECTIVE GAS SHIELD APPARATUS/Neil; Stoddard, Yuh	200107153-9 05/19/00	Singapore
FE	67588	EP	AJT. MSS	PROTECTIVE GAS SHIELD APPARATUS/Stoddard, Yuh	89109705 05/19/00	Taiwan
FP	67588	PC	AJT.	PROTECTIVE GAS SHIELD APPARATUS/Stoddard, Yuh	00936074.4 05/19/00	Europe
				PROTECTIVE GAS SHIELD APPARATUS/Stoddard, Yuh	PCT/US00/13754 closed	PCT

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Reference No.			Title/Inventors		Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
		MSS	Yuh		05/19/00		
P	67588	-I AJT MSS	REPLACEABLE VENT SHIELD SHIM		Unfiled		
P	67735	AJT MSS	IMPROVED TRENCH ISOLATION PROCESS USING APCVD TEOS-OZONE TO DEPOSIT A TRENCH FILL OXIDE PRIOR TO SIDEWALL LINER OXIDATION GROWTH/Curtis; Rao; Kaplan		60/127,520 04/02/99	Closed	
A	67735	AJT MSS	IMPROVED TRENCH ISOLATION PROCESS USING APCVD TEOS-OZONE TO DEPOSIT A TRENCH FILL OXIDE PRIOR TO SIDEWALL LINER OXIDATION GROWTH/Curtis; Rao; Kaplan		09/541,395 03/31/00	6,387,764 Issued: 05/14/02	
FA	67735	CA AJT MSS	TRENCH ISOLATION PROCESS USING APCVD TEOS-OZONE TO DEPOSIT A TRENCH FILL OXIDE PRIOR TO SIDEWALL LINER OXIDATION GROWTH/Curtis; Rao; Kaplan		2364975 03/31/00	Abandoned	Canada
FA	67735	CN AJT MSS	TRENCH ISOLATION PROCESS USING APCVD TEOS-OZONE TO DEPOSIT A TRENCH FILL OXIDE PRIOR TO SIDEWALL LINER OXIDATION GROWTH/Curtis; Rao; Kaplan		00807742.8 03/31/00		China
FA	67735	IL AJT MSS	TRENCH ISOLATION PROCESS USING APCVD TEOS-OZONE TO DEPOSIT A TRENCH FILL OXIDE PRIOR TO SIDEWALL LINER OXIDATION GROWTH/Curtis; Rao; Kaplan Rao		145608 03/31/00	Abandoned	Israel
FA	67735	JP AJT MSS	TRENCH ISOLATION PROCESS USING APCVD TEOS-OZONE TO DEPOSIT A TRENCH FILL OXIDE PRIOR TO SIDEWALL LINER OXIDATION GROWTH/Curtis; Rao; Kaplan		2000-610059 03/31/00		Japan
FA	67735	KR AJT MSS	TRENCH ISOLATION PROCESS USING APCVD TEOS-OZONE TO DEPOSIT A TRENCH FILL OXIDE PRIOR TO SIDEWALL LINER OXIDATION GROWTH/Curtis; Rao; Kaplan		2001-7012564 03/31/00		South Korea
FA	67735	SG AJT MSS	TRENCH ISOLATION PROCESS USING APCVD TEOS-OZONE TO DEPOSIT A TRENCH FILL OXIDE PRIOR TO SIDEWALL LINER OXIDATION GROWTH/Curtis; Rao; Kaplan		200105864-3 03/31/00		Singapore

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Reference No.			Title/Inventors		Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
FA	67735	TW	AJT MSS	TRENCH ISOLATION PROCESS USING APCVD TEOS-OZONE TO DEPOSIT A TRENCH FILL OXIDE PRIOR TO SIDEWALL LINER OXIDATION GROWTH/ Curtis; Rao; Kaplan	89106191 04/01/00		Taiwan
FE	67735	EP	AJT MSS	TRENCH ISOLATION PROCESS USING APCVD TEOS-OZONE TO DEPOSIT A TRENCH FILL OXIDE PRIOR TO SIDEWALL LINER OXIDATION GROWTH/ Curtis; Rao; Kaplan	00919996.9 03/31/00		
FP	67735	PC	AJT MSS	TRENCH ISOLATION PROCESS USING APCVD TEOS-OZONE TO DEPOSIT A TRENCH FILL OXIDE PRIOR TO SIDEWALL LINER OXIDATION GROWTH/ Curtis; Rao; Kaplan	PCT/US00/08650 03/31/00		PCT
P	67736		AJT MSS VEJ	NEAR-ATMOSPHERIC CVD SYSTEM WITH VERTICALLY-STACKED PROCESS CHAMBERS/ Carvalho; Mayer; Menagh; Savage; Vaughan	60/127,532 04/02/99	Closed	
A	67736		AJT MSS VEJ	SEMICONDUCTOR WAFER PROCESS SYSTEM WITH VERTICALLY-STACKED PROCESS CHAMBERS AND SINGLE-AXIS DUAL-WAFER TRANSFER SYSTEM/Savage; Menagh; Carvalho; Troiani; Cosentino; Vaughan; Mayer	09/483,945 01/13/00	6,610,150 08/26/03	
FA	67736	CA	AJT MSS	SEMICONDUCTOR WAFER PROCESSING SYSTEM WITH VERTICALLY-STACKED PROCESS CHAMBERS AND SINGLE-AXIS DUAL-WAFER TRANSFER SYSTEM/Savage; Menagh; Carvalho; Troiani; Cosentino; Vaughan; Mayer	2369042 03/21/00	Abandoned	Canada
FA	67736	CN	AJT MSS	SEMICONDUCTOR WAFER PROCESSING SYSTEM WITH VERTICALLY-STACKED PROCESS CHAMBERS AND SINGLE-AXIS DUAL-WAFER TRANSFER SYSTEM/Savage; Menagh; Carvalho; Troiani; Cosentino; Vaughan; Mayer	008006652.3 03/21/00		China
FA	67736	IL	AJT MSS	SEMICONDUCTOR WAFER PROCESSING SYSTEM WITH VERTICALLY-STACKED PROCESS CHAMBERS AND SINGLE-AXIS DUAL-WAFER TRANSFER SYSTEM/Savage; Menagh; Carvalho; Troiani; Cosentino; Vaughan; Mayer	145678 03/21/00	Abandoned	Israel

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Reference No.			Title/Inventors		Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
FA	67736	JP	AJT MSS	SEMICONDUCTOR WAFER PROCESSING SYSTEM WITH VERTICALLY-STACKED PROCESS CHAMBERS AND SINGLE-AXIS DUAL-WAFER TRANSFER SYSTEM/Savage; Menagh; Carvalheira; Troiani; Cossetine; Vaughan; Mayer	2000-609844 03/21/00		Japan
FA	67736	KR	AJT MSS	SEMICONDUCTOR WAFER PROCESSING SYSTEM WITH VERTICALLY-STACKED PROCESS CHAMBERS AND SINGLE-AXIS DUAL-WAFER TRANSFER SYSTEM/Savage; Menagh; Carvalheira; Troiani; Cossetine; Vaughan; Mayer	2001-7012462 03/21/00		South Korea
FA	67736	SG	AJT MSS	SEMICONDUCTOR WAFER PROCESSING SYSTEM WITH VERTICALLY-STACKED PROCESS CHAMBERS AND SINGLE-AXIS DUAL-WAFER TRANSFER SYSTEM/Savage; Menagh; Carvalheira; Troiani; Cossetine; Vaughan; Mayer	200105951-8 03/21/00		Singapore
FA	67736	TW	AJT MSS VEJ	SEMICONDUCTOR WAFER PROCESS SYSTEM WITH VERTICALLY-STACKED PROCESS CHAMBERS AND SINGLE-AXIS DUAL-WAFER TRANSFER SYSTEM/Savage; Menagh; Carvalheira; Troiani; Cossetine; Vaughan; Mayer	89106019 03/31/00		Taiwan
FE	67736	EP	AJT MSS JTW	SEMICONDUCTOR WAFER PROCESSING SYSTEM WITH VERTICALLY-STACKED PROCESS CHAMBERS AND SINGLE-AXIS DUAL-WAFER TRANSFER SYSTEM/Savage; Menagh; Carvalheira; Troiani; Cossetine; Vaughan; Mayer	0091829.7 03/21/00		Europe
FP	67736	PC	AJT MSS VEJ	SEMICONDUCTOR WAFER PROCESS SYSTEM WITH VERTICALLY-STACKED PROCESS CHAMBERS AND SINGLE-AXIS DUAL-WAFER TRANSFER SYSTEM/Savage; Menagh; Carvalheira; Troiani; Cossetine; Vaughan; Mayer	PCT/US00/07509 03/21/00	Closed	PCT
A	67736	1	AJT MSS	SEMICONDUCTOR WAFER PROCESS SYSTEM WITH VERTICALLY-STACKED PROCESS CHAMBERS AND SINGLE-AXIS DUAL-WAFER TRANSFER SYSTEM/Savage; Menagh; Carvalheira; Troiani; Cossetine; Vaughan; Mayer	09/767,659 01/22/01 Divisional of 09/483,945 filed 01/13/00		
A	67736	2	AJT	SEMICONDUCTOR WAFER PROCESSING SYSTEM WITH VERTICALLY-STACKED PROCESS	09/996,869		

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Reference No.		Title/Inventors		Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
		MSS	CHAMBERS AND SINGLE-AXIS DUAL-WAFER TRANSFER SYSTEM/Savage; Mcnough; Carvalho; Troiani; Cossethine; Vaughan; Meyer	11/27/01		
P	67737	AJT MSS VEJ	SINGLE-AXIS DUAL-WAFER TRANSFER SYSTEM/Troiani; Cossethine	60/127,650 04/02/99	Merged into P-67736 & Closed	
P	68017	AJT MSS WEN	IMPROVED SURFACE COMPOSITION AND METHOD FOR METAL COMPONENTS/Bailey; Michael; Kano	60/130,783 04/23/99	Closed	
A	68017	AJT MSS WEN	CHEMICAL VAPOR DEPOSITION SYSTEM/Bailey; Michael; Kano	09/480,730 01/06/00	6,206,973 03/27/01	
FA	68017	CA MSS WEN	CHEMICAL VAPOR DEPOSITION SYSTEM/Bailey; Michael; Kano	2371353 03/03/00	Abandoned	Canada
FA	68017	CN MSS WEN	CHEMICAL VAPOR DEPOSITION SYSTEM/Bailey; Michael; Kano	0080854.4 03/03/00		China
FA	67017	IL MSS WEN	CHEMICAL VAPOR DEPOSITION SYSTEM/Bailey; Michael; Kano	146135 03/03/00	Abandoned	Israel
FA	68017	JP MSS WEN	CHEMICAL VAPOR DEPOSITION SYSTEM/Bailey; Michael; Kano	2000-613851 03/03/00		Japan
FA	68017	KR MSS WEN	CHEMICAL VAPOR DEPOSITION SYSTEM/Bailey; Michael; Kano	2001-7013598 03/03/00		South Korea
FA	68017	SG MSS WEN	CHEMICAL VAPOR DEPOSITION SYSTEM/Bailey; Michael; Kano	20010613-5 03/03/00		Singapore
FA	68017	TW AJT MSS WEN	CHEMICAL VAPOR DEPOSITION SYSTEM/Bailey; Michael; Kano	89104518 03/13/00		Taiwan
FB	68017	EP AJT MSS WEN	CHEMICAL VAPOR DEPOSITION SYSTEM/Bailey; Michael; Kano	00912173.2 03/03/00		Europe
FP	68017	PC AJT MSS WEN	CHEMICAL VAPOR DEPOSITION SYSTEM/Bailey; Michael; Kano	PCT/US00/03630 03/03/00	Closed	PCT
A	68017	1 AJT MSS	CHEMICAL VAPOR DEPOSITION SYSTEM AND METHOD/Bailey; Michael; Kano	09/704,644 11/01/00	6,485,783	

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Reference No.		Title/Inventors		Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
P	68048	WEN			11/26/02	
		AJT MSS WEN	EQUAL FLOW SPLIT GAS DELIVERY APPARATUS/Bartholomew, Yuh; Stumbo; King; Chan	60/134,443 05/17/99	Closed	
A	68048	AJT MSS WEN	GAS DISTRIBUTION SYSTEM/Bartholomew, Yuh; Stumbo; King; Chan	09/494,620 01/31/00	Abandoned	
FA	68048	CA	GAS DISTRIBUTION SYSTEM/Bartholomew, Yuh; Stumbo; King; Chan	2308832 05/15/00	Abandoned	Canada
FA	68048	CN	GAS DISTRIBUTION SYSTEM/Bartholomew, Yuh; Stumbo; King; Chan	00108349.2 05/17/00		China
FE	68048	EP	GAS DISTRIBUTION SYSTEM/Bartholomew, Yuh; Stumbo; King; Chan	00304070.6 05/15/00		Europe
FA	68048	HK	GAS DISTRIBUTION SYSTEM/Bartholomew, Yuh; Stumbo; King; Chan	01102640.9 04/12/01	Abandoned	Hong Kong
FA	68048	JP	GAS DISTRIBUTION SYSTEM/Bartholomew, Yuh; Stumbo; King; Chan	2000-144513 05/17/00		Japan
FA	68048	KR	GAS DISTRIBUTION SYSTEM/Bartholomew, Yuh; Stumbo; King; Chan	2000-0026027 05/16/00		South Korea
FA	68048	MY	GAS DISTRIBUTION SYSTEM/Bartholomew, Yuh; Stumbo; King; Chan	PI20002031 05/10/00		Malaysia
FA	68048	SG	GAS DISTRIBUTION SYSTEM/Bartholomew, Yuh; Stumbo; King; Chan	200002470-3 05/09/00	87112 10/16/02	Singapore
FA	68048	TH	GAS DISTRIBUTION SYSTEM/Bartholomew, Yuh; Stumbo; King; Chan	057634 05/16/00	Abandoned	Thailand
FA	68048	TW	GAS DISTRIBUTION SYSTEM/Bartholomew, Yuh; Stumbo; King; Chan	89109368		Taiwan

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Reference No.		Title/Inventors		Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
		MSS WEN	Stumbe, King, Chan	05/16/00		
A	68048	I MSS WEN	GAS DISTRIBUTION SYSTEM/Bartholomew, Yuh; Mark, King, Chan	10/21/924 08/14/02	Abandoned	
P	68073	AJT MSS	CHEMICAL VAPOR DEPOSITION OF SILICON DIOXIDE BY USING ALKYL SILOXANE OLIGOMERS WITH OZONE FOR SUB 0.18 MICRON DEVICE APPLICATIONS IN VLSI/Jain; Yuan	60/143,198 07/09/99	Closed	
A	68073	AJT MSS	CHEMICAL VAPOR DEPOSITION OF SILICON DIOXIDE BY USING ALKYL SILOXANE OLIGOMERS WITH OZONE FOR SUB 0.18 MICRON DEVICE APPLICATIONS IN VLSI/Jain; Yuan	09/542,612 04/04/00	6465044 10/15/02	
FA	68073	CN AJT MSS	CHEMICAL VAPOR DEPOSITION OF SILICON OXIDE FILMS USING ALKYL SILOXANE OLIGOMERS WITH OZONE/Jain; Yuan	00811030.1 06/15/00		China
FA	68073	JP AJT MSS	CHEMICAL VAPOR DEPOSITION OF SILICON OXIDE FILMS USING ALKYL SILOXANE OLIGOMERS WITH OZONE/Jain; Yuan	2001-509075 06/15/00		Japan
FA	68073	KR AJT MSS	CHEMICAL VAPOR DEPOSITION OF SILICON OXIDE FILMS USING ALKYL SILOXANE OLIGOMERS WITH OZONE/Jain; Yuan	2002-7000308 06/15/00		South Korea
FA	68073	SG AJT MSS	CHEMICAL VAPOR DEPOSITION OF SILICON OXIDE FILMS USING ALKYL SILOXANE OLIGOMERS WITH OZONE/Jain; Yuan	06/15/00		Singapore
FA	68073	TW AJT MSS	CHEMICAL VAPOR DEPOSITION OF SILICON OXIDE FILMS USING ALKYL SILOXANE OLIGOMERS WITH OZONE/Jain; Yuan	89113435 07/06/00	153183 07/25/02	Taiwan
FE	68073	EP AJT MSS	CHEMICAL VAPOR DEPOSITION OF SILICON OXIDE FILMS USING ALKYL SILOXANE OLIGOMERS WITH OZONE/Jain; Yuan	00939940.3 06/15/00		Europe
FP	68073	PC AJT MSS	CHEMICAL VAPOR DEPOSITION OF SILICON OXIDE FILMS USING ALKYL SILOXANE OLIGOMERS WITH OZONE/Jain; Yuan	PCT/US00/16642 06/15/00	Closed	PCT
P	68244	AJT	METHOD FOR IN-SITU CLEANING OF SILICON	60/143,285	Closed	

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Reference No.		Title/Inventors		Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
		MSS		07/12/99		
A	68244			09/615,035 07/12/00	6,544,345 04/08/03	
FA	68244	CN		00811232.0 07/12/00		China
FA	68244	JP		2001-509320 07/12/00		Japan
FA	68244	KR		2002-7000480 07/12/00		South Korea
FA	68244	SG		200200181-6 07/12/00		Singapore
FA	68244	TW		89113887 07/18/00		Taiwan
FE	68244	EP		00958006.9 07/12/00		Europe
FP	68244	PC		PCT/US00/40359 07/12/00	Closed	PCT
P	68628			60/166,662	Closed	

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Reference No.		Title/Inventors		Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
A	68628	MSS	INORGANIC/ORGANIC DIELECTRIC FILMS/Lopata; Felts	11/19/99		
FA	68628	AJT MSS	SYSTEM AND METHOD FOR DEPOSITING INORGANIC/ORGANIC DIELECTRIC FILMS/Lopata; Felts	09/715,455 11/17/00		
FA	68628	CN AJT MSS	SYSTEM AND METHOD FOR DEPOSITING INORGANIC/ORGANIC DIELECTRIC FILMS/Lopata; Felts	00816928.4 11/17/00		China
FA	68628	JP AJT MSS	SYSTEM AND METHOD FOR DEPOSITING INORGANIC/ORGANIC DIELECTRIC FILMS/Lopata; Felts	2001-538578 11/17/00		Japan
FA	68628	KR AJT MSS	SYSTEM AND METHOD FOR DEPOSITING INORGANIC/ORGANIC DIELECTRIC FILMS/Lopata; Felts	11/17/00		South Korea
FA	68628	MY AJT MSS	SYSTEM AND METHOD FOR DEPOSITING INORGANIC/ORGANIC DIELECTRIC FILMS/Lopata; Felts	P120005431 11/20/00		Malaysia
FA	68628	SG AJT MSS	SYSTEM AND METHOD FOR DEPOSITING INORGANIC/ORGANIC DIELECTRIC FILMS/Lopata; Felts	11/17/00		Singapore
FA	68628	TW AJT MSS	SYSTEM AND METHOD FOR DEPOSITING INORGANIC/ORGANIC DIELECTRIC FILMS/Lopata; Felts	89124488 11/18/00		Taiwan
FB	68628	EP AJT MSS	SYSTEM AND METHOD FOR DEPOSITING INORGANIC/ORGANIC DIELECTRIC FILMS/Lopata; Felts	00980511.0 11/17/00		Europe
FP	68628	PC AJT MSS	SYSTEM AND METHOD FOR DEPOSITING INORGANIC/ORGANIC DIELECTRIC FILMS/Lopata; Felts	PCT/US00/31694 11/17/00	Closed	PCT
A	68894		CHEMICAL VAPOR DEPOSITION APPARATUS/Campbell; Miller	06/412,237 08/12/82	4,545,327 10/08/85	
FA	68894	AU AJT MSS	CHEMICAL VAPOR DEPOSITION APPARATUS AND PROCESS/Campbell; Miller	18480/83 08/26/83	538152 08/26/83 Abandoned	Australia
FA	68894	CA AJT MSS	CHEMICAL VAPOR DEPOSITION APPARATUS AND PROCESS/Campbell; Miller	435,134 08/23/83	1,196,777 11/19/85	Canada

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Reference No.			Title/Inventors		Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
FA	68894	IL	AJT MSS	CHEMICAL VAPOR DEPOSITIONS PROCESS/ Campbell; Miller	69170 07/06/83	Abandoned	
FA	68894	IL-1	AJT MSS	CHEMICAL VAPOR DEPOSITION PROCESS/ Campbell; Miller	80079 07/06/83	Abandoned	Israel
FA	68894	JP	AJT MSS	CHEMICAL VAPOR DEPOSITION APPARATUS AND PROCESS/Campbell; Miller	155171/83 08/26/83	Abandoned	Israel
FE	68894	EP	AJT MSS	CHEMICAL VAPOR DEPOSITION APPARATUS AND PROCESS/Campbell; Miller	83304889.5	Abandoned	Japan
A	68894	I	AJT MSS	CHEMICAL VAPOR DEPOSITION APPARATUS AND PROCESS/Campbell; Miller	06/657,313 10/02/84	Abandoned	Europe
A	68895		AJT MSS	CHEMICAL VAPOR DEPOSITION APPARATUS/ Campbell; DuBois; Manriquez; Miller	06/528,193 08/31/83	4,547,404 10/15/85	
FA	68895	AU	AJT MSS	CHEMICAL VAPOR DEPOSITION APPARATUS/ Campbell; DuBois; Manriquez; Miller	3256484 08/30/84	4,539,933 09/10/85	
FA	68895	CA	AJT MSS	CHEMICAL VAPOR DEPOSITION APPARATUS/ Campbell; DuBois; Manriquez; Miller	462,110 08/30/84	572,883 08/30/84 Abandoned	Australia
FA	68895	CA-1	AJT MSS	CHEMICAL VAPOR DEPOSITION APPARATUS/ Campbell; DuBois; Manriquez; Miller	515,262 08/01/86	1,216,419 01/13/87 Abandoned	Canada
FA	68895	TW	AJT MSS	CHEMICAL VAPOR DEPOSITION APPARATUS/ Campbell; DuBois; Manriquez; Miller	73103,596 08/30/84	1,236,970 05/24/88 Abandoned	Canada
FE	68895	EP	AJT MSS	CHEMICAL VAPOR DEPOSITION APPARATUS/ Campbell; DuBois; Manriquez; Miller	84305932.0 08/30/84	23307 12/28/85 Abandoned	Taiwan
A	68896		AJT MSS	CHEMICAL VAPOR DEPOSITION APPARATUS/ Foster; Herring	06/628,542 07/06/84	0137702 03/21/90 Abandoned	Europe
FA	68896	JP	AJT MSS	CHEMICAL VAPOR DEPOSITION WAFER BOAT/ Foster; Herring	146857/85 07/05/85	4,548,159 10/22/85 1451172 07/25/88 Abandoned	Japan

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Reference No.			Title/Inventors		Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
A	68897	AJT MSS		CHEMICAL VAPOR DEPOSITION WAFER BOAT/ Learn; DuBois	06/607,065 05/04/84	4,582,020 04/15/86	
FA	68897	CA AJT MSS		CHEMICAL VAPOR DEPOSITION WAFER BOAT/ Learn; DuBois	480,118 04/25/85	1,234,972 04/12/88 Abandoned	Canada
FA	68897	JP AJT MSS		CHEMICAL VAPOR DEPOSITION WAFER BOAT/ Learn; DuBois	93957/85 05/02/85	1,604,459 04/22/91	Japan
A	68897	1 AJT MSS		CHEMICAL VAPOR DEPOSITION WAFER BOAT/ Learn; DuBois	06/804,954 12/05/85 Continuation of 06/607,065	4,641,604 02/10/87 Abandoned	
A	68897	2 AJT MSS		CHEMICAL VAPOR DEPOSITION WAFER BOAT/ Learn; DuBois	06/828,625 02/10/86 Continuation of 06/607,065	4,694,778 09/22/87 Abandoned	
A	68898	AJT MSS		PRIMARY FLOW CVD APPARATUS COMPRISING GAS PREHEATER AND MEANS FOR SUBSTANTIALLY EDDY-FREE GAS FLOW/Learn; DuBois; Miller; Sellheimer	07/691,470 04/25/91	5,320,680 06/14/94	
FA	68898	CA AJT MSS		PRIMARY FLOW CVD APPARATUS AND METHOD/ Learn; DuBois; Miller; Sellheimer	2,109,198 04/09/92	2109198 03/28/00 Abandoned	Canada
FA	68898	JP AJT MSS		PRIMARY FLOW CVD APPARATUS AND METHOD/ Learn; DuBois; Miller; Sellheimer	510862/92 04/09/92	3193716 05/25/01	Japan
FA	68898	KR AJT MSS		PRIMARY FLOW CVD APPARATUS AND METHOD/ Learn; DuBois; Miller; Sellheimer	703234/1993 10/25/93	0267520 07/05/00	South Korea
FE	68898	CH AJT MSS		PRIMARY FLOW CVD APPARATUS AND METHOD/ Learn; DuBois; Miller; Sellheimer	92911855.2 04/09/92	0585343 12/08/99 Abandoned	Switzerland
FE	68898	DE AJT MSS		PRIMARY FLOW CVD APPARATUS AND METHOD/ Learn; DuBois; Miller; Sellheimer	92911855.2 04/09/92	69230401.0 12/08/99	Germany
FE	68898	EP AJT MSS		PRIMARY FLOW CVD APPARATUS AND METHOD/ Learn; DuBois; Miller; Sellheimer	92911855.2 04/09/92	0585343 12/08/99	Europe
FE	68898	FR AJT		PRIMARY FLOW CVD APPARATUS AND METHOD/ Learn; DuBois; Miller; Sellheimer	92911855.2	0585343	France

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Reference No.			Title/Inventors		Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
FE	68898	GB	MSS	Learn; DuBois; Miller; Sellheimer	04/09/92	12/08/99	
FE	68898	IT	AJT	PRIMARY FLOW CVD APPARATUS AND METHOD/ Learn; DuBois; Miller; Sellheimer	92911855.2 04/09/92	0585343 12/08/99	United Kingdom
FE	68898	NL	MSS	PRIMARY FLOW CVD APPARATUS AND METHOD/ Learn; DuBois; Miller; Sellheimer	92911855.2 04/09/92	0585343 12/08/99	Italy
FP	68898	PC	AJT	PRIMARY FLOW CVD APPARATUS AND METHOD/ Learn; DuBois; Miller; Sellheimer	92911855.2 04/09/92	0585343 12/08/99	Netherlands
A	68899		MSS	PRIMARY FLOW CVD APPARATUS AND METHOD/ Learn; DuBois; Miller; Sellheimer	PCT/US92/02666 04/09/92	Closed	PCT
A	68899	1	AJT	THERMAL PROCESSING APPARATUS AND PROCESS/Porter; Sanchez; Kowalski	08/399,108 03/03/95	5,626,680 05/06/97	
FP	68899	1-PC	MSS	THERMAL PROCESSING APPARATUS AND PROCESS/Porter; Sanchez; Kowalski	08/399,108 03/03/95	5,679,168 10/21/97	
FE	68899	1-EP	AJT	THERMAL PROCESSING APPARATUS AND PROCESS/Porter; Sanchez; Kowalski	PCT/US96/02440 03/04/96	Closed	PCT
FA	68899	1-JP	MSS	THERMAL PROCESSING APPARATUS AND PROCESS/Porter; Sanchez; Kowalski	96906398.6 03/04/96		Europe
FA	68899	1-KR	AJT	THERMAL PROCESSING APPARATUS AND PROCESS/Porter; Sanchez; Kowalski	526893/96 09/01/97		Japan
A	68899	2	MSS	THERMAL PROCESSING APPARATUS AND PROCESS/Kobla, Jr.; Dip; Engdahl; Oliver; Radliff	706100/1997 09/02/97		South Korea
FP	68899	2-PC	AJT	THERMAL PROCESSING APPARATUS AND PROCESS/Kobla, Jr.; Dip; Engdahl; Oliver; Radliff	08/563,875 11/28/95	5,618,351 04/08/97	
FE	68899	2-EP	MSS	THERMAL PROCESSING APPARATUS AND PROCESS/Kobla, Jr.; Dip; Engdahl; Oliver; Radliff	CIP of 08/399,108 11/22/96	Closed	PCT
FA	68899	2-JP	AJT	THERMAL PROCESSING APPARATUS AND PROCESS/Kobla, Jr.; Dip; Engdahl; Oliver; Radliff	96941440.8 11/22/96	0864170	Europe
FA	68899	2-KR	MSS	THERMAL PROCESSING APPARATUS AND PROCESS/Kobla, Jr.; Dip; Engdahl; Oliver; Radliff	520363/97 11/22/96		Japan
				THERMAL PROCESSING APPARATUS AND PROCESS/Kobla, Jr.; Dip; Engdahl; Oliver; Radliff	703960/1998 11/22/96		South Korea

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Reference No.			Title/Inventors		Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
FA	68899	2-TW	AJT MSS	THERMAL PROCESSING APPARATUS AND PROCESS/Kobbe, Jr.; Dtp; Engdahl; Oliver; Radtiff	86101168 01/31/97	NL-094773 06/11/98	Taiwan
A	68900		AJT MSS	METHOD OF LOADING AND UNLOADING A FURNACE/Aldridge; Elloway; Fritz; Goff; Herrera	06/719,409 04/03/85	4,636,140 01/13/87	
A	68900	1	AJT MSS	SEMICONDUCTOR WAFER BOAT LOADER RELEASABLE MOUNTING/Aldridge; Elloway; Fritz; Goff; Herrera	06/880,460 06/30/86 Div. of 06/719,409	4,721,424 01/26/88 Abandoned Reinstated	
A	68900	2	AJT MSS	SEMICONDUCTOR WAFER FURNACE DOOR/ Aldridge; Elloway; Fritz; Goff; Herrera	06/880,422 06/30/86 Div. of 06/719,409	4,692,115 09/08/87 Abandoned	
A	68900	3	AJT MSS	SEMICONDUCTOR WAFER BOAT LOADER CONTROL SYSTEM	06/880,423 06/30/86 Div. of 06/719,409	4,684,863 08/04/87 Abandoned	
A	68901		AJT MSS	GAS SCAVENGER/Taylor	06/919,736 10/16/86	4,711,197 12/08/87 Abandoned	
FA	68901	CA	AJT MSS	GAS SCAVENGER/Taylor	545,025 08/21/87	1,277,442 12/04/90 Abandoned	Canada
FA	68901	JP	AJT MSS	GAS SCAVENGER/Taylor	261507/87 10/16/87	2642936 05/02/97	Japan
A	68902		AJT MSS	THERMAL PROCESSING APPARATUS/Kowalski; Radtiff; Kobbe; Peck; Yang	08/827,542 03/28/97	6,005,225 12/21/99	
FA	68902	KR	AJT MSS	THERMAL PROCESSING APPARATUS/Kowalski; Radtiff; Kobbe; Peck; Yang	10787/1998 03/27/98		South Korea
FA	68902	JP	AJT MSS	THERMAL PROCESSING APPARATUS/Kowalski; Radtiff; Kobbe; Peck; Yang	951866/98 03/25/98		Japan
FA	68902	TW	AJT MSS	THERMAL PROCESSING APPARATUS/Kowalski; Radtiff; Kobbe; Peck; Yang	87104418 03/24/98		Taiwan
FE	68902	EP	AJT MSS	THERMAL PROCESSING APPARATUS/Kowalski; Radtiff; Kobbe; Peck; Yang	98301618.9 03/05/98		Europe
A	68902	1	AJT	SEMICONDUCTOR THERMAL PROCESSOR WITH	09/022,057	6,059,567	

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1059128

Reference No.		Title/Inventors		Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
FA	68902	MSS	RECIRCULATING HEATER EXHAUST COOLING SYSTEM/Bolton; Wiesen	02/10/98 CIP of 08/827,542	05/09/00	
FA	68902	1-AU AJT MSS	SEMICONDUCTOR THERMAL PROCESSOR RECIRCULATING HEATER/Bolton; Wiesen	1551/99 02/08/99		Australia
FE	68902	1-CA AJT MSS	SEMICONDUCTOR THERMAL PROCESSOR RECIRCULATING HEATER/Bolton; Wiesen	2,261,391 02/08/99		Canada
FE	68902	1-EP AJT MSS	SEMICONDUCTOR THERMAL PROCESSOR RECIRCULATING HEATER/Bolton; Wiesen	99300910.9 02/09/99		Europe
FE	68902	1-HK AJT MSS	SEMICONDUCTOR THERMAL PROCESSOR RECIRCULATING HEATER/Bolton; Wiesen	00100999.1 02/18/00		Hong Kong
FA	68902	1-JP AJT MSS	SEMICONDUCTOR THERMAL PROCESSOR RECIRCULATING HEATER/Bolton; Wiesen	11-072438 02/10/99		Japan
FA	68902	1-KR AJT MSS	SEMICONDUCTOR THERMAL PROCESSOR RECIRCULATING HEATER/Bolton; Wiesen	4492/1999 02/09/99		South Korea
A	68903	AJT MSS/WEN	DOUBLE WALL REACTION CHAMBER GLASSWARE/Fowler; Parvin; Kowalaki; Wiesen	09/022,056 02/10/98	6,101,844 08/15/00	
FA	68903	AU AJT MSS	DOUBLE WALL REACTION CHAMBER GLASSWARE/Fowler; Parvin; Kowalaki; Wiesen	15512/99 02/08/99	746022 07/25/02	Australia
FA	68903	CA AJT MSS	DOUBLE WALL REACTION CHAMBER GLASSWARE/Fowler; Parvin; Kowalaki; Wiesen	2,261,394 02/08/99	Abandoned	Canada
FA	68903	JP AJT MSS	DOUBLE WALL REACTION CHAMBER GLASSWARE/Fowler; Parvin; Kowalaki; Wiesen	11-072437 02/10/99		Japan
FA	68903	KR AJT MSS	DOUBLE WALL REACTION CHAMBER GLASSWARE/Fowler; Parvin; Kowalaki; Wiesen	4491/1999 02/09/99		South Korea
FE	68903	EP AJT MSS	DOUBLE WALL REACTION CHAMBER GLASSWARE/Fowler; Parvin; Kowalaki; Wiesen	99300909.1 02/09/99		Europe
FE	68903	HK AJT MSS	DOUBLE WALL REACTION CHAMBER GLASSWARE/Fowler; Parvin; Kowalaki; Wiesen	00100998.2 02/18/00	Abandoned	Hong Kong
P	68905	AJT MSS	LINEAR RPT. REACTOR/Kowalaki; Ratiff; Suh; Qin	60/096,283 08/12/98	Closed	
A	68905	AJT MSS	HOT WALL RAPID THERMAL PROCESSOR/Ratiff; Qin; Kowalaki; Yadollahi; Sedghi	09/373,894 08/12/99	6,300,600 10/09/01	
P	68905	1 AJT	HOT WALL RAPID THERMAL PROCESSOR/Ratiff	60/217,321	Closed	

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Reference No.		Title/Inventors		Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
A	68905	1	MSS			
			AJT	07/07/00		
FP	68905	1-PC	MSS	09/638,113	6,462,310	
			AJT	08/11/00	10/08/02	
EA	68905	1-CN	MSS	PCT/US90/22202	Closed	PCT
			AJT	08/11/00		
FA	68905	1-JP	MSS	00812823.5		China
			MBG	08/11/00		
FA	68905	1-KR	AJT	2001-517110		Japan
			MSS	08/11/00		
FA	68905	1-MY	MBG			South Korea
			AJT	2002-7001786		
FA	68905	1-SG	MSS	08/11/00		Malaysia
			AJT	P1 20003683		
FA	68905	1-TW	MSS	08/11/00		Singapore
			MBG	Unfiled		
FB	68905	1-EP	AJT	89116281	149415	Taiwan
			MSS	08/11/00	05/17/02	
A	68905	2	AJT	00957426.0		Europe
			MSS	08/11/00		
A	68905	3	MSS	09/934,952	6,492,621	
			AJT	08/21/01	12/10/02	
A	68905	4	MSS	10/262,215		
			AJT	09/30/02		
A	68905	5	MSS	10/261,963		
			AJT	09/30/02		
A	68906		AJT		Unfiled	
			MSS	06/529,415	4,324,719	
A	68907		AJT	09/06/83	06/25/85	
			AJT	06/899,923	4,720,395	
			AJT			

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Reference No.		Title/Inventors		Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
		MSS	PROCESS	08/23/86	01/19/88	
A	68908	AJT MSS	PULSE WIDTH MODULATED PRESSURE CONTROL SYSTEM FOR CHEMICAL VAPOR DEPOSITION APPARATUS/Johnson; Elliott	06/845,212 03/27/86 CIP of 06/813,915	Abandoned 4,728,869 03/01/88	
A	68909	AJT MSS	HOT WALL DIFFUSION FURNACE AND METHOD FOR OPERATING THE FURNACE/Yt; Fisk; Emami	07/181,787 04/15/88	4,886,954 12/12/89	
A	68910	AJT MSS	METHOD AND APPARATUS FOR REMOVAL OF BY- PRODUCTS OF CHEMICAL VAPOR DEPOSITION FROM OIL FOR VACUUM PUMP/Foster	06/029,525 04/12/79	4,228,004 10/14/80	
A	68911	AJT MSS	MASS FLOW CONTROLLER/Doyle	06/193,876 10/03/80	4,658,855 04/21/87	
A	68912	AJT MSS	DIFFUSION FURNACE MULTIZONE TEMPERATURE CONTROL/Yu	06/864,676 05/19/86	4,711,989 12/08/87	
A	68913	AJT MSS	WAFER BOAT TRANSFER TOOL/Mello	06/863,963 05/16/86	4,728,246 03/01/88	
A	68914	AJT MSS	WAFER TRANSFER STAND/Sanders; Taylor	07/048,868 05/12/87	Abandoned 4,721,427 01/26/88	
A	68915	AJT MSS	TEMPERATURE SENSOR FOR BATCH-TYPE REACTOR/Radiff	09/024,500 02/17/98	Abandoned Reinstated Abandoned	
A	68916	AJT MSS VEI	LAYERED BLOCK FLUID DELIVERY SYSTEM/ Nguyen	09/388,216 09/01/99	Abandoned	
PA	68916	TW AJT MSS	LAYERED BLOCK FLUID DELIVERY SYSTEM/M'guyen	89116370 08/14/00	148378 08/21/01	Taiwan
FP	68916	PC AJT MSS	LAYERED BLOCK FLUID DELIVERY SYSTEM/M'guyen	US0021227 08/03/00	Abandoned	PCT

Reference No.		Title/Inventors		Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
A	68916	1	AJT MSS VEJ	MODULAR FLUID DELIVERY SYSTEM/Nguyen	09/800,595 03/06/01 CIP of 09/388,216 09/01/99	
FA	68916	1-CN	AJT MSS	MODULAR FLUID DELIVERY APPARATUS/Nguyen	02106830.5 03/05/02	China
FA	68916	1-JP	AJT MSS	MODULAR FLUID DELIVERY APPARATUS/Nguyen	2002-059114 03/05/02	Japan
FA	68916	1-KR	AJT MSS	MODULAR FLUID DELIVERY APPARATUS/Nguyen	2002-0011854 03/06/02	South Korea
FA	68916	1-MY	AJT MSS	MODULAR FLUID DELIVERY APPARATUS/Nguyen	P120020747 03/01/02	Malaysia
FA	68916	1-SG	AJT MSS	MODULAR FLUID DELIVERY APPARATUS/Nguyen	200201201-1 02/27/02	Singapore
FA	68916	1-TW	AJT MSS	MODULAR FLUID DELIVERY APPARATUS/Nguyen	91103478 02/26/02	Taiwan
FE	68916	1-EP	AJT MSS	MODULAR FLUID DELIVERY APPARATUS/Nguyen	02251573.8 03/06/02	Europe
P	69013		MSS	FLUOROPOLYMER INTERLAYER DIELECTRIC BY CHEMICAL VAPOR DEPOSITION/Rose; Brichko; Lopata; Mocella	05/04/01 (filed by Du Pont)	Co-owned with DuPont
A	69013		AJT MSS	DEPOSITION OF FLUOROPOLYMER FILMS/Mocella; Rose; Lopata; Pacak; Talley; Young	Unfiled	
A	69173		MSS	MODEL BASED TEMPERATURE CONTROL OF BATCH FURNACE/Oh	Unfiled	
A	69174		MSS	IN-SITU METHOD AND APPARATUS FOR END POINT DETECTION IN CHEMICAL MECHANICAL POLISHING/Nam; Saka; Oh	09/628,471 07/31/00	Co-owned with MIT, all foreign as well
P	69174	1	MSS	IN-SITU SENSING AND ENDPOINT DETECTION IN COPPER CMP/Saka; Lai; Oh	60/258,931 12/29/00	
A	69174	1	AJT MSS	IN-SITU METHOD AND APPARATUS FOR END POINT DETECTION IN CHEMICAL MECHANICAL POLISHING/Saka; Lai; Oh	10/029,080 12/21/01	Co-owned with MIT, all foreign as well

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Reference No.			Title/Inventors		Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
FA	69174	I-CN	MSS	IN-SITU METHOD AND APPARATUS FOR END POINT DETECTION	N/A		China
FA	69174	I-JP	MSS	IN-SITU METHOD AND APPARATUS FOR END POINT DETECTION	2002-516606 01/31/01		Japan
FA	69174	I-KR	MSS	IN-SITU METHOD AND APPARATUS FOR END POINT DETECTION	2003-7001394 01/31/01		S. Korea
FA	69174	I-MY	AJT MSS	IN-SITU METHOD AND APPARATUS FOR END POINT DETECTION IN CHEMICAL MECHANICAL POLISHING/Name; Sub; Oh	PI 20013602 07/31/01		Malaysia
FA	69174	I-SG	MSS	IN-SITU METHOD AND APPARATUS FOR END POINT DETECTION	200300662-4 01/31/01		Singapore
FA	69174	I-TW	MSS	IN-SITU METHOD AND APPARATUS FOR END POINT DETECTION IN CHEMICAL MECHANICAL POLISHING/Name; Sub; Oh	90118624 07/31/01	158247 10/18/02	Taiwan
FP	69174	I-PC	MSS	IN-SITU METHOD AND APPARATUS FOR END POINT DETECTION IN CHEMICAL MECHANICAL POLISHING/Name; Sub; Oh	PCT/US01/24146 07/31/01	Closed	PCT
A	69175		MSS	APPARATUS AND METHOD FOR CHEMICAL MECHANICAL POLISHING OF SUBSTRATES/Melvin; Sub; Oh	09/628,563 07/31/00		Co-owned with MIT, all foreign as well
FA	69175	MY	MSS	APPARATUS AND METHOD FOR CHEMICAL MECHANICAL POLISHING OF SUBSTRATES/Melvin; Sub; Oh	PI20013601 07/30/01		Malaysia
FA	69175	TW	MSS	APPARATUS AND METHOD FOR CHEMICAL MECHANICAL POLISHING OF SUBSTRATES/Melvin; Sub; Oh	90118623 07/31/01		Taiwan
P	69175	I	MSS	APPARATUS AND METHOD FOR CHEMICAL MECHANICAL POLISHING OF SUBSTRATES/Melvin; Sub; Oh	60259,016 12/29/00	Closed	
				APPARATUS AND METHOD FOR CHEMICAL MECHANICAL POLISHING OF SUBSTRATES/Sub; Melvin; Oh	20030158 12/21/01		Co-owned with MIT, all foreign as well
FA	69175	I-CN	MSS	APPARATUS AND METHOD FOR CHEMICAL MECHANICAL POLISHING	01815145.0 01/31/01		China

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Reference No.			Title/Inventors		Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
FA	69175	1-JP	MSS	APPARATUS AND METHOD FOR CHEMICAL MECHANICAL POLISHING	2002-515445 01/31/01		Japan
FA	69175	1-KR	MSS	APPARATUS AND METHOD FOR CHEMICAL MECHANICAL POLISHING	2003-7001395 01/31/01		South Korea
FA	69175	1-SG	MSS	APPARATUS AND METHOD FOR CHEMICAL MECHANICAL POLISHING	200300678-0 01/31/01		Singapore
FA	69175	1-EP	MSS	APPARATUS AND METHOD FOR CHEMICAL MECHANICAL POLISHING	19623362 01/31/01		Europe
FP	69175	1-PC	MSS	APPARATUS AND METHOD FOR CHEMICAL MECHANICAL POLISHING OF SUBSTRATES/Melvin; Sub; Oh	PCT/US01/41513 07/31/01		PCT
A	69175	2	MSS	APPARATUS AND METHOD FOR CHEMICAL MECHANICAL POLISHING OF SUBSTRATES/Sub; Melvin; Oh	Closed		
A	69228		MSS	METHOD OF CHEMICAL MECHANICAL POLISHING/Lat; Saba; Oh	09/628,962 07/31/00	6,458,013 10/01/02	Co-owned with MIT, all foreign as well
FA	69228	CN	MSS	METHOD OF CHEMICAL MECHANICAL POLISHING/Lat; Saba; Oh	01815147.7 07/31/01		China
FA	69228	JP	MSS	METHOD OF CHEMICAL MECHANICAL POLISHING/Lat; Saba; Oh	2002-515446 07/31/01		Japan
FA	69228	KR	MSS	METHOD OF CHEMICAL MECHANICAL POLISHING/Lat; Saba; Oh	2003-7001400 07/31/01		South Korea
FA	69228	MY	MSS	METHOD OF CHEMICAL MECHANICAL POLISHING/Lat; Saba; Oh	P20013603 07/31/01		Malaysia
FP	69228	PC	MSS	METHOD OF CHEMICAL MECHANICAL POLISHING/Lat; Saba; Oh	PCT/US01/24170 07/31/01		PCT
FA	69228	SG	MSS	METHOD OF CHEMICAL MECHANICAL POLISHING/Lat; Saba; Oh	200300663-2 07/31/01		Singapore
FA	69228	TW	MSS	METHOD OF CHEMICAL MECHANICAL POLISHING/Lat; Saba; Oh	90118625 07/31/01		Taiwan
FE	69228	EP	MSS	METHOD OF CHEMICAL MECHANICAL POLISHING/Lat; Saba; Oh	01957381.5 07/31/01		Europe
P	69229		MSS	MECHANISMS OF MATERIAL REMOVAL IN THE CHEMICAL MECHANICAL POLISHING PROCESS/	60263,813 01/23/01	Closed	

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Reference No.		Title/Inventors		Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
		Lai; Saka; Chinn				
A	69229	MSS		10057,477 01/23/02		Co-owned with MIT; all foreign as will
FP	69229	PC	MSS	PCT/US02/02254 01/23/02		PCT
A	69274		MSS	06/864,077 05/16/86	4,770,590 09/13/88	
RB	69274		MSS	90/006,018 05/21/01	Re-examination of Patent No. 4,770,590	
FA	69274	DE	MSS	P3715601.2 05/09/87	315787 07/06/00	Germany
FA	69274	DE-1	MSS	P3745134.0 01/24/96	03/04/99	Germany
FA	69274	FR	MSS	8706851 05/15/87	8706851 08/21/92	France
FA	69274	FR-1	MSS	8716024 11/19/87	8716024 08/21/92	France
FA	69274	IT	MSS	479304/87 05/14/87	1206283 04/14/89	Italy
FA	69274	JP	MSS	62-117197 05/15/87	2681055 08/08/97	Japan
FA	69274	GB	MSS	8711230 05/13/87	2190345 08/15/90	Great Britain
FA	69274	GB-1	MSS	8922730.0 05/13/87	2223470 08/15/90	Great Britain

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Reference No.		Title/Inventors		Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
A	69404		MSS	NON-CONTACT CMP MACHINE		
P	69447		MSS	SYSTEM AND METHOD TO CONTROL RADIAL DELTA-T/Porter; Stamer	60/274,532 03/08/01	
A	69447		MSS	SYSTEM AND METHOD TO CONTROL RADIAL DELTA TEMPERATURE- -T/Porter; Stamer	10/095,974 03/08/02	
FP	69447	PC	MSS	SYSTEM AND METHOD TO CONTROL RADIAL DELTA TEMPERATURE- -T/Porter; Stamer	PCT/US02/07034 03/08/02	PCT
FA	69447	CN	MSS	SYSTEM AND METHOD TO CONTROL RADIAL DELTA TEMPERATURE- -T/Porter; Stamer	02800595.3 03/08/02	China
FA	69447	JP	MSS	SYSTEM AND METHOD TO CONTROL RADIAL DELTA TEMPERATURE- -T/Porter; Stamer	2002/572612 03/08/02	Japan
FA	69447	KR	MSS	SYSTEM AND METHOD TO CONTROL RADIAL DELTA TEMPERATURE- -T/Porter; Stamer	2002-7014904 03/08/02	South Korea
FA	69447	MY	MSS	SYSTEM AND METHOD TO CONTROL RADIAL DELTA TEMPERATURE- -T/Porter; Stamer	P20022469 06/28/02	Malaysia
FA	69447	SG	MSS	SYSTEM AND METHOD TO CONTROL RADIAL DELTA TEMPERATURE- -T/Porter; Stamer	200206968-0 03/08/02	Singapore
FA	69447	TW	MSS	SYSTEM AND METHOD TO CONTROL RADIAL DELTA TEMPERATURE- -T/Porter; Stamer	91114419 06/25/02	Taiwan
FE	69447	EP	MSS	SYSTEM AND METHOD TO CONTROL RADIAL DELTA TEMPERATURE- -T/Porter; Stamer	027079649 03/08/02	Europe
P	69448		MSS	INERTIAL TEMPERATURE CONTROL/Stamer	60/266,926 02/06/01	Closed
A	69448		MSS	INERTIAL TEMPERATURE CONTROL/Stamer	10/068,127 02/06/02	
FA	69448	CN	MSS	INERTIAL TEMPERATURE CONTROL/Stamer	021080852 02/06/02	China
FA	69448	JP	MSS	INERTIAL TEMPERATURE CONTROL/Stamer	2002-069336 02/06/02	Japan
FA	69448	KR	MSS	INERTIAL TEMPERATURE CONTROL/Stamer	2002-6778 02/06/02	South Korea
FA	69448	MY	MSS	INERTIAL TEMPERATURE CONTROL/Stamer	P20020366 02/24/02	Malaysia

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Reference No.			Title/Inventors		Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
FA	69448	SG	MSS	INERTIAL TEMPERATURE CONTROL/Starnet	200200733-4 02/06/02		Singapore
FA	69448	TW	MSS	INERTIAL TEMPERATURE CONTROL/Starnet	91101797 02/01/02	173549 07/07/03	Taiwan
FE	69448	EP	MSS	INERTIAL TEMPERATURE CONTROL/Starnet	02250814.7 02/06/02		Europe
A	69477		MSS	NON-CONTACT CMP MACHINE/Suh		Closed	
P	69829		MSS	APPARATUS FOR THE PREFERENTIAL DEPOSITION OF TEOS+O3 BASED SIOX THIN FILMS ON SILICON SURFACES RELATIVE TO SILICON-NITRIDE SURFACES/Mayer; Ingles; Murphy; Mattoon; Kurita	60335494 11/01/01	Closed	
A	69829		MSS MDV	APPARATUS FOR THE PREFERENTIAL DEPOSITION OF TEOS+O3 BASED SIOX THIN FILMS ON SILICON SURFACE RELATIVE TO SILICON-NITRIDE SURFACES/Mayer; Ingles; Murphy; Mattoon; Kurita	10285966 11/01/02		
FA	69829	CN	MSS MDV MBG	APPARATUS FOR THE PREFERENTIAL DEPOSITION OF TEOS+O3 BASED SIOX THIN FILMS ON SILICON SURFACES RELATIVE TO SILICON-NITRIDE SURFACES/Mayer; Ingles; Murphy; Mattoon; Kurita	11/01/02		China
FA	69829	JP	MSS MDV MBG	APPARATUS FOR THE PREFERENTIAL DEPOSITION OF TEOS+O3 BASED SIOX THIN FILMS ON SILICON SURFACES RELATIVE TO SILICON-NITRIDE SURFACES/Mayer; Ingles; Murphy; Mattoon; Kurita	2002-320226 11/01/02		Japan
FA	69829	KR	MSS MDV MBG	APPARATUS FOR THE PREFERENTIAL DEPOSITION OF TEOS+O3 BASED SIOX THIN FILMS ON SILICON SURFACES RELATIVE TO SILICON-NITRIDE SURFACES/Mayer; Ingles; Murphy; Mattoon; Kurita	10/31/02		South Korea
FA	69829	MY	MSS MDV MBG	APPARATUS FOR THE PREFERENTIAL DEPOSITION OF TEOS+O3 BASED SIOX THIN FILMS ON SILICON SURFACES RELATIVE TO SILICON-NITRIDE SURFACES/Mayer; Ingles; Murphy; Mattoon; Kurita	PI20024020 10/28/02		Malaysia

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Reference No.			Title/Inventors		Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
FA	69829	SG	MSS MDV MBG	APPARATUS FOR THE PREFERENTIAL DEPOSITION OF TEOS+O3 BASED SIOX THIN FILMS ON SILICON SURFACES RELATIVE TO SILICON-NITRIDE SURFACES/Mayer; Inglet; Murphy; Matheson; Kurita	200206557-1 10/28/02		Singapore
FA	69829	TW	MSS MDV MBG	APPARATUS FOR THE PREFERENTIAL DEPOSITION OF TEOS+O3 BASED SIOX THIN FILMS ON SILICON SURFACES RELATIVE TO SILICON-NITRIDE SURFACES/Mayer; Inglet; Murphy; Matheson; Kurita	91125270 10/25/02		Taiwan
FE	69829	EP	MSS MDV MBG	APPARATUS FOR THE PREFERENTIAL DEPOSITION OF TEOS+O3 BASED SIOX THIN FILMS ON SILICON SURFACES RELATIVE TO SILICON-NITRIDE SURFACES/Mayer; Inglet; Murphy; Matheson; Kurita	02257608.6 01/01/02		Europe
P	70028		MSS	MULTILAYER HIGH DIELECTRIC CONSTANT OXIDE FILMS AND METHOD OF MAKING/Senzaki	60264,428 01/26/01	Closed	
A	70028		MSS	MULTILAYER HIGH-x GATE OXIDE THIN FILMS/Senzaki	10/056,625 01/25/02		
P	70292		AJT MSS	FLUOROPOLYMER INTERLAYER DIELECTRIC BY CHEMICAL VAPOR DEPOSITION/Mocella; Feiring, Treat, Brichko, Lopata, Rose	60/288,653 05/04/01	Closed	Application is co- owned with DuPont To be filed by DuPont counsel
			No Dosey Ref. number.	FLUOROPOLYMER INTERLAYER DIELECTRIC BY CHEMICAL VAPOR DEPOSITION/Lopata; Mocella	10/137,875 May 2, 2002		Application is co- owned with DuPont To be filed by DuPont counsel
P	70380		MSS MDV	HIGH FLOW RATE BUBBLER WITH A LIQUID PHASE EVAPORATOR/Tockman	60/337,566 11/30/01	Closed	
A	70380		MSS MDV	HIGH FLOW RATE BUBBLER WITH A LIQUID PHASE EVAPORATOR/Tockman			
FA	70380	MY	MSS	HIGH FLOW RATE BUBBLER SYSTEM AND METHOD; Tockman	11/27/02 P1 20024434 11/27/02		Malaysia

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Reference No.			Title/Inventors		Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
FA	70380	TW	MSS	HIGH FLOW RATE BUBBLER SYSTEM AND METHOD; Torkman	91134329 11/26/02		Taiwan
FA	70380	PC	MSS	HIGH FLOW RATE BUBBLER SYSTEM AND METHOD; Torkman	US02/38178 11/27/03		PCT.
P	70381		MSS WEN	APPARATUS AND METHOD FOR INSULATING A SEAL IN A PROCESS CHAMBER/Draper; Robinson; Lopes	60/313,719 08/20/01	Closed	
A	70381		MSS WEN	APPARATUS & METHOD FOR INSULATING A SEAL IN A PROCESS CHAMBER/Draper; Robinson; Lopes	10/224,687 08/20/02		
FA	70381	CN	MSS	APPARATUS & METHOD FOR INSULATING A SEAL IN A PROCESS CHAMBER/Draper; Robinson; Lopes	02143456.5 08/19/02		China
FA	70381	JP	MSS	APPARATUS & METHOD FOR INSULATING A SEAL IN A PROCESS CHAMBER/Draper; Robinson; Lopes	2002-280066 08/20/02		Japan
FA	70381	KR	MSS	APPARATUS & METHOD FOR INSULATING A SEAL IN A PROCESS CHAMBER/Draper; Robinson; Lopes	2002-0049154 08/20/02		South Korea
FA	70381	MY	MSS	APPARATUS & METHOD FOR INSULATING A SEAL IN A PROCESS CHAMBER/Draper; Robinson; Lopes	P120023060 08/19/02		Malaysia
FA	70381	SG	MSS	APPARATUS & METHOD FOR INSULATING A SEAL IN A PROCESS CHAMBER/Draper; Robinson; Lopes	200205046-6 08/20/02		Singapore
FA	70381	TW	AJT MSS MBG	SYSTEM AND METHOD FOR DEPOSITING INORGANIC/ORGANIC DIELECTRIC FILMS/Draper; Robinson; Lopes	91118697 08/19/02		Taiwan
FE	70381	EP	MSS	APPARATUS & METHOD FOR INSULATING A SEAL IN A PROCESS CHAMBER/Draper; Robinson; Lopes	02255775.5 08/20/02		Europe
A	70466		MSS	CHEMICAL VAPOR DEPOSITION SYSTEM FOR DEPOSITING FLUOROPOLYMER FILMS/Lopaia	Closed		
P	70524		MSS	MODULAR INJECTOR AND EXHAUST ASSEMBLY/ DeDontley; Mathiesen; Kurita	60/305,406 07/13/01	Closed	
A	70524		MSS	MODULAR INJECTOR AND EXHAUST ASSEMBLY/ DeDontley; Mathiesen; Kurita	10/194,639 07/12/02		
FA	70524	CN	MSS TJH MBG	MODULAR INJECTOR/DeDontley; Mathiesen; Kurita	02141805.5 07/15/02		China

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Reference No.			Title/Inventors		Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
FA	70524	JP	MSS TJH MBG	MODULAR INJECTOR/DeDontley; Matthiesen; Kurita	2002-205716 07/15/02		Japan
FA	70524	KR	MSS TJH MBG	MODULAR INJECTOR/DeDontley; Matthiesen; Kurita	2002-0040964 07/13/02		South Korea
FA	70524	MY	MSS TJH MBG	MODULAR INJECTOR/DeDontley; Matthiesen; Kurita	PI20022636 07/11/02		Malaysia
FA	70524	SG	MSS TJH MBG	MODULAR INJECTOR/DeDontley; Matthiesen; Kurita	200204228-1 07/12/02		Singapore
FA	70524	TW	MSS TJH MBG	MODULAR INJECTOR/DeDontley; Matthiesen; Kurita	91115568 07/12/02		Taiwan
FE	70524	EP	MSS TJH	MODULAR INJECTOR/DeDontley; Matthiesen; Kurita	02254963.8 07/15/02		Europe
A	70824		MSS	HEATING SYSTEM AND METHOD FOR HEATING AN ATMOSPHERIC REACTION/Breeden; Seidemann; Koesler	Prepared and Prosecuted by Infineon counsel	This patent appln. is co-owned with Infineon	[related opened matrices: Pat. Appl. # MY- 0P120021354; TW-091107447; PC- PCT/EP02/04060]
P	70859		MSS	DEPOSITION OF LOW STRESS GERMANIUM AND BORON DOPED SILICA FILMS FOR OPTICAL WAVEGUIDES/Mogard	60/310,026 08/03/01	Closed	
A	70859		MSS	OXIDE STRUCTURE AND METHOD OF FORMING THE OXIDE STRUCTURE/Mogard	10/210,978 08/02/02		
FA	70859	CN	MSS	OXIDE STRUCTURE USEABLE FOR OPTICAL WAVEGUIDE AND METHOD OF FORMING THE OXIDE STRUCTURE/Mogard	08/08/02		China
FA	70859	JP	MSS	OXIDE STRUCTURE USEABLE FOR OPTICAL WAVEGUIDE AND METHOD OF FORMING THE OXIDE STRUCTURE/Mogard	2002-262112 08/05/02		Japan
FA	70859	KR	MSS	OXIDE STRUCTURE USEABLE FOR OPTICAL	2002-0045980		South Korea

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Reference No.		Title/Inventors		Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
FA	70859	MY	MSS	WAVEGUIDE AND METHOD OF FORMING THE OXIDE STRUCTURE/ Mogard	08/03/02	
FA	70859	SG	MSS	OXIDE STRUCTURE USEABLE FOR OPTICAL WAVEGUIDE AND METHOD OF FORMING THE OXIDE STRUCTURE/ Mogard	PI20022907 08/02/02	Malaysia
FA	70859	TW	MSS	OXIDE STRUCTURE USEABLE FOR OPTICAL WAVEGUIDE AND METHOD OF FORMING THE OXIDE STRUCTURE/ Mogard	2002046711-2 08/02/02	Singapore
FE	70859	EP	MSS MDV MBG	OXIDE STRUCTURE USEABLE FOR OPTICAL WAVEGUIDE AND METHOD OF FORMING THE OXIDE STRUCTURE/ Mogard	91117477 08/02/02	Taiwan
A	70888		MSS TJH	DEPOSITION OF LOW STRESS GERMANIUM AND BORON DOPED SILICA FILMS FOR OPTICAL WAVEGUIDES/Mogard	02255429.9 08/02/02	Europe
P	70893		MSS	BELLOWS ROTARY FEED-THROUGH SEAL/ Hs Yuh	Closed	
A	70893		MSS	AN IMPROVED DESIGN FOR A LINEAR INJECTOR ASSEMBLY/ Mattson; Hakmelahy; Bartholomew; Pate; Yuh	60/314,762 08/24/01	Closed
FA	70893	MY	MSS MBG	PROTECTIVE SHIELD AND SYSTEM FOR GAS DISTRIBUTION SYSTEM/Mattson; Hakmelahy; Bartholomew; Pate; Yuh	10/226,459 08/23/02	
FA	70893	TW	MSS MBG	DESIGN FOR A LINEAR INJECTOR ASSEMBLY/ Mattson; Hakmelahy; Bartholomew; Pate; Yuh	PI20023124 08/23/02	Malaysia
FP	70893	PC	MSS	DESIGN FOR A LINEAR INJECTOR ASSEMBLY/ Mattson; Hakmelahy; Bartholomew; Pate; Yuh	91119174 08/23/02	Taiwan
P	70896		MSS	PROTECTIVE SHIELD AND SYSTEM FOR GAS DISTRIBUTION/Mattson; Hakmelahy; Bartholomew; Pate; Yuh	PCT/US0227376 08/26/02	PCT
A	70896		MSS	ATMOSPHERIC PRESSURE WAFER PROCESSING REACTOR HAVING AN INTERNAL PRESSURE CONTROL SYSTEM AND METHOD/Bartholomew; Bailey; Pate; Yuh	60/314,760 08/24/01	Closed
				ATMOSPHERIC PRESSURE WAFER PROCESSING REACTOR HAVING AN INTERNAL PRESSURE	10/226,773 08/23/02	

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Reference No.			Title/Inventors		Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
FA	70896	MY	MSS MBG	CONTROL SYSTEM AND METHOD/Bartholomew; Bailey, Park; Yuh			
FA	70896	TW	MSS MBG	ATMOSPHERIC PRESSURE WAFER PROCESSING REACTOR HAVING AN INTERNAL PRESSURE CONTROL SYSTEM AND METHOD/Bartholomew; Bailey, Park; Yuh	P20023123 08/23/02		Malaysia
FP	70896	PC	MSS	ATMOSPHERIC PRESSURE WAFER PROCESSING REACTOR HAVING AN INTERNAL PRESSURE CONTROL SYSTEM AND METHOD/Bartholomew; Bailey, Park; Yuh	91119175 08/23/02		Taiwan
P	71033		MSS	ATMOSPHERIC PRESSURE WAFER PROCESSING REACTOR HAVING AN INTERNAL PRESSURE CONTROL SYSTEM AND METHOD/Bartholomew; Bailey, Park; Yuh	PCT/US02/27372 08/26/02		PCT
A	71033		MSS	APPARATUS AND PROCESS FOR IMPROVED THIN DIELECTRIC FILMS/Senzaki; Herring; Helms; Osborne	60332,397 11/16/01	Closed	
FA	71033	CN	MSS JW	SYSTEM AND METHOD FOR IMPROVED THIN DIELECTRIC FILMS/Senzaki; Herring; Helms; Osborne	10/106,677 03/25/02		
FA	71033	JP	MSS JW	SYSTEM AND METHOD FOR IMPROVED THIN DIELECTRIC FILMS/Senzaki; Herring; Helms; Osborne	02157580.0 11/15/02		China
FA	71033	KR	MSS JW	SYSTEM AND METHOD FOR IMPROVED THIN DIELECTRIC FILMS/Senzaki; Herring; Helms; Osborne	2002-333209 11/18/02		Japan
FA	71033	MY	MSS JW	SYSTEM AND METHOD FOR IMPROVED THIN DIELECTRIC FILMS/Senzaki; Herring; Helms; Osborne	2002-0071019 11/15/02		South Korea
FA	71033	SG	MSS JW	SYSTEM AND METHOD FOR IMPROVED THIN DIELECTRIC FILMS/Senzaki; Herring; Helms; Osborne	FI 20024197 11/11/02		Malaysia
FA	71033	TW	MSS	SYSTEM AND METHOD FOR IMPROVED THIN DIELECTRIC FILMS/Senzaki; Herring; Helms; Osborne	200206876-5 11/14/02		Singapore
FE	71033	EP	MSS JW	SYSTEM AND METHOD FOR IMPROVED THIN DIELECTRIC FILMS/Senzaki; Herring; Helms; Osborne	91133057 11/11/02		Taiwan
				SYSTEM AND METHOD FOR IMPROVED THIN DIELECTRIC FILMS/Senzaki; Herring; Helms; Osborne	02257838.9 11/13/02		Europe

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Reference No.			Title/Inventors		Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
A	71033	1	MSS	SYSTEM AND METHOD FOR IMPROVED THIN DIELECTRIC FILMS/Senzaki; Herring; Helms; Osborne	Closed		
A	71090		MSS	OPTIMIZATION OF CHEMICAL REACTION RATE COEFFICIENTS BY AUTOMATED ITERATIVE COMPUTER SIMULATIONS AND COEFFICIENT VARIATION USING A DESIGNED-EXPERIMENT. APPROACH/Chatham; Bailey	Closed		
P	71181		MSS	HEATED VACUUM SUPPORT APPARATUS Tom Kane, Jeff Bailey, Sam Kurita, Kris Veeck	60/333,447 11/26/01	Closed	
A	71181		MSS TJH	HEATED VACUUM SUPPORT APPARATUS/Kane; Bailey; Kurita; Veeck	10/303,035 11/22/02		
FA	71181	MY	MSS	HEATED VACUUM SUPPORT APPARATUS/Kane, Bailey; Kurita; Veeck	PI 2002/4390 11/25/02		Malaysia
FA	71181	TW	MSS	HEATED VACUUM SUPPORT APPARATUS/Kane; Bailey; Kurita; Veeck	91134187 11/25/02		Taiwan
FP	71181	PC	MSS	HEATED VACUUM SUPPORT APPARATUS/Kane; Bailey; Kurita; Veeck	PCT/US02/38106 11/25/02		PCT
P	71197		MSS	IN-SITU THERMAL CHAMBER CLEANING/Herring; Slason; Senzaki	60/379,381 03/09/02	Closed	
A	71197		MSS TJH	SINGLE WAFER THERMAL PROCESSING SYSTEM AND IN-SITU CLEANING METHOD/Herring; Slason; Senzaki	10/318,664 12/12/02		
FA	71197	MY	MSS	SINGLE WAFER THERMAL PROCESSING SYSTEM AND IN-SITU CLEANING METHOD/Herring; Slason; Senzaki	PI 20031610 04/29/03		Malaysia
FA	71197	TW	MSS	SINGLE WAFER THERMAL PROCESSING SYSTEM AND IN-SITU CLEANING METHOD/Herring; Slason; Senzaki	92110202 04/30/03		Taiwan
FA	71197	PC	MSS	SINGLE WAFER THERMAL PROCESSING SYSTEM AND IN-SITU CLEANING METHOD/Herring; Slason; Senzaki	N/A 04/25/03		PCT
A	71355		MSS	SEMICONDUCTOR WAFER CARRIER TRANSPORT APPARATUS/Hoyt III; Sanders; Goldman; Mello	06/863,961 05/16/86	4,722,659 02/02/88	

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Reference No.		Title/Inventors		Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
A	71356	MSS	SEMICONDUCTOR WAFER CARRIER INPUT/ OUTPUT DRAWER/Hoyt III; Goldman; Mello	06/863,960 05/16/86	Abandoned 4,934,767 06/19/90	
P	71514	MSS	METHOD OF DEPOSITING AN OXIDE FILM BY CHEMICAL VAPOR DEPOSITION TO ACHIEVE COMPLETE GAP-FILL SUB-MICRON STRUCTURES/ Park; Bartholomew; Yuh	60/382,780 05/21/02	Abandoned Closed	
A	71514	MSS	METHOD OF DEPOSITING AN OXIDE FILM BY CHEMICAL VAPOR DEPOSITION/ Park; Bartholomew; Yuh	10/442,423 05/20/03		
FA	71514 MY	MSS	METHOD OF DEPOSITING AN OXIDE FILM BY CHEMICAL VAPOR DEPOSITION/ Park; Bartholomew; Yuh	PI 20031855 05/20/03		Malaysia
FA	71514 TW	MSS	METHOD OF DEPOSITING AN OXIDE FILM BY CHEMICAL VAPOR DEPOSITION/ Park; Bartholomew; Yuh	05/20/03		Taiwan
FP	71514 PC	MSS	METHOD OF DEPOSITING AN OXIDE FILM BY CHEMICAL VAPOR DEPOSITION/ Park; Bartholomew; Yuh	05/20/03		PCT
P	71564	MSS	SYSTEM AND METHOD FOR HYDROGEN RICH SELECTIVE OXIDATION/Herring; Porter; Dodwell; Nazzareno; Radloff; Chatterji	60/387,185 06/06/02	Closed	
A	71564	MSS	SYSTEM AND METHOD FOR HYDROGEN RICH SELECTIVE OXIDATION/Herring; Porter; Dodwell; Nazzareno; Radloff; Chatterji	10/456,850 06/06/03		
FA	71564 MY	MSS	SYSTEM AND METHOD FOR HYDROGEN RICH SELECTIVE OXIDATION/Herring; Porter; Dodwell; Nazzareno; Radloff; Chatterji	06/06/03		Malaysia
FA	71564 TW	MSS	SYSTEM AND METHOD FOR HYDROGEN RICH SELECTIVE OXIDATION/Herring; Porter; Dodwell; Nazzareno; Radloff; Chatterji	06/06/03		Taiwan

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Reference No.			Title/Inventors		Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
FP	71564	PC	MSS	SYSTEM AND METHOD FOR HYDROGEN RICH SELECTIVE OXIDATION/Herring; Porter, Dodwell; Nezarenoy; Rediff; Chatterji	06/06/03		PCT
P	71581		MSS	OZONE OXIDATION OF SILICON SUBSTRATES FOR FORMATION OF AN INTERFACIAL LAYER FOR HIGH-k GATE STACKS/Senzaki; Herring	60/399,463 07/29/02	Closed	
A	71581		MSS	OZONE OXIDATION OF SILICON SUBSTRATES FOR FORMATION OF AN INTERFACIAL LAYER FOR HIGH-k GATE STACKS/Senzaki; Herring			Unfiled
FP	71581	PC	MSS	OZONE OXIDATION OF SILICON SUBSTRATES FOR FORMATION OF AN INTERFACIAL LAYER FOR HIGH-k GATE STACKS/Senzaki; Herring	07/29/03		PCT
FA	71581	TW	MSS	OZONE OXIDATION OF SILICON SUBSTRATES FOR FORMATION OF AN INTERFACIAL LAYER FOR HIGH-k GATE STACKS/Senzaki; Herring	07/29/03		Taiwan
P	71582		MSS WEN	OPTIMIZED MINI-BATCH CONFIGURABLE VERTICAL CHAMBER/Qu; Wildman; Collins; Kowalecki; Edwards; DuBois; Nam; Torkaman; Ma; Stamer	60/396,536 07/15/02	Closed	
P	71582	1	MSS WEN	OPTIMIZED MINI-BATCH CONFIGURABLE VERTICAL CHAMBER/Qu; Wildman; Collins; Kowalecki; Edwards; DuBois; Nam; Torkaman; Ma; Stamer	60/428,526 11/22/02	Closed	
P	71606		MSS	SYSTEM AND METHOD FOR ATOMIC LAYER DEPOSITION AND REMOVAL/Kapkin; Sang-In Lee	60/391,011 06/23/02	Closed	
A	71606		MSS TTH	METHOD AND SYSTEM FOR ATOMIC LAYER DEPOSITION/Kapkin; Sang-In Lee			
FA	71606	TW	MSS	SYSTEM AND METHOD FOR ATOMIC LAYER DEPOSITION AND REMOVAL/Kapkin; Sang-In Lee	06/23/03		Taiwan
FP	71606	PC	MSS	SYSTEM AND METHOD FOR ATOMIC LAYER DEPOSITION AND REMOVAL/Kapkin; Sang-In Lee	PCT/US03/19982 06/23/03		PCT
P	71606	1	MSS	METHOD AND SYSTEM FOR PHOTO-ASSISTED ATOMIC LAYER DEPOSITION AND REMOVAL/ Helms, Jr.; Kapkin; Sang-In Lee; Senzaki	60/391,012 06/23/02	Closed	

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Reference No.			Title/Inventors		Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
FA	71606	I-TW MSS	METHOD AND SYSTEM FOR PHOTO-ASSISTED ATOMIC LAYER DEPOSITION AND REMOVAL/ Hsiao, Jr.; Kaplan; Sang-In Lee; Senzaki		06/23/03		Taiwan
FP	71606	I-PC MSS	METHOD AND SYSTEM FOR PHOTO-ASSISTED ATOMIC LAYER DEPOSITION AND REMOVAL/ Hsiao, Jr.; Kaplan; Sang-In Lee; Senzaki		06/23/03		PCT
P	71622		MOLECULAR LAYER DEPOSITION OF THIN FILMS WITH MIXED COMPONENTS/Senzaki; Sang-In Lee	60/397,029 07/18/02	Closed		
A	71622		MOLECULAR LAYER DEPOSITION OF THIN FILMS WITH MIXED COMPONENTS/Senzaki; Sang-In Lee				
FA	71622	TW MSS	MOLECULAR LAYER DEPOSITION OF THIN FILMS WITH MIXED COMPONENTS/Senzaki; Sang-In Lee	07/16/03			Taiwan
FP	71622	PC MSS	MOLECULAR LAYER DEPOSITION OF THIN FILMS WITH MIXED COMPONENTS/Senzaki; Sang-In Lee	92119581 07/17/03			PCT
P	71637		AFNEX MACH 2 WAFER HEATING & TRANSLATE SYSTEM & DESIGN/DaDontney	60/396,735 07/19/02	Closed		
P	71638		ATOMIC LAYER DEPOSITION OF HIGH-k DIELECTRIC FILMS/Senzaki; Sang-In Lee	60/396,723 07/19/02	Closed		
A	71638		ATOMIC LAYER DEPOSITION OF HIGH-k DIELECTRIC FILMS/Senzaki; Sang-In Lee				
FA	71638	TW MSS	ATOMIC LAYER DEPOSITION OF HIGH-k DIELECTRIC FILMS/Senzaki; Sang-In Lee	07/17/03			Taiwan
FP	71638	PC MSS	ATOMIC LAYER DEPOSITION OF HIGH-k DIELECTRIC FILMS/Senzaki; Sang-In Lee	07/19/03			PCT
P	71639		LOW TEMPERATURE OZONE ANNEAL OF GATE AND CAPACITOR DIELECTRICS/Senzaki; Sang-In Lee	60/396,742 07/19/02	Closed		
FA	71639	TW MSS	LOW TEMPERATURE OZONE ANNEAL OF GATE AND CAPACITOR DIELECTRICS/Senzaki; Sang-In Lee	07/17/03			Taiwan
FP	71639	PCT MSS	LOW TEMPERATURE OZONE ANNEAL OF GATE AND CAPACITOR DIELECTRICS/Senzaki; Sang-In Lee	07/16/03			PCT

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Reference No.		Title/Inventors		Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
P	71640	MSS	LOW TEMPERATURE DIELECTRIC DEPOSITION USING AMINOSILANE AND OZONE/Senzaki	60/396,746 07/19/02	Closed	
FA	71640	TW	LOW TEMPERATURE DIELECTRIC DEPOSITION USING AMINOSILANE AND OZONE/Senzaki			
FP	71640	PC	LOW TEMPERATURE DIELECTRIC DEPOSITION USING AMINOSILANE AND OZONE/Senzaki	07/17/03		Taiwan
P	71641	MSS	LOW TEMPERATURE DIELECTRIC DEPOSITION USING AMINOSILANE AND OZONE/Senzaki	07/15/03		PCT
A	71641	MSS	MOCVD & ATOMIC LAYER DEPOSITION OF HF-O- N & H ₂ Si-O-N FOR GATE AND CAPACITOR DIELECTRICS/Senzaki; Sang-In Lee	60/396,744 07/19/02	Closed	
FA	71641	TW	MOCVD & ATOMIC LAYER DEPOSITION OF HF-O- N & H ₂ Si-O-N FOR GATE AND CAPACITOR DIELECTRICS/Senzaki; Sang-In Lee			
FP	71641	PC	MOCVD & ATOMIC LAYER DEPOSITION OF HF-O- N & H ₂ Si-O-N FOR GATE AND CAPACITOR DIELECTRICS/Senzaki; Sang-In Lee	92119583 07/17/03		Taiwan
P	71642	MSS	MOCVD & ATOMIC LAYER DEPOSITION OF HF-O- N & H ₂ Si-O-N FOR GATE AND CAPACITOR DIELECTRICS/Senzaki; Sang-In Lee	07/16/03		PCT
P	71643	MSS	VACUUM UV ASSISTED ATOMIC LAYER DEPOSITION/Senzaki; Sang-In Lee	60/396,743 07/19/02	Closed, combined with 71606-1	
FA	71643	TW	STEAM OXIDATION FOR THE FORMATION OF THIN GATE AND CAPACITOR DIELECTRIC WITH IMPROVED ELECTRICAL PROPERTIES/Senzaki; Brichko; Herring	60/396,733 07/19/02	Closed	
FP	71643	PC	STEAM OXIDATION FOR THE FORMATION OF THIN GATE AND CAPACITOR DIELECTRIC WITH IMPROVED ELECTRICAL PROPERTIES/Senzaki; Brichko; Herring	07/17/073		Taiwan
FP	71643	MSS	STEAM OXIDATION FOR THE FORMATION OF THIN GATE AND CAPACITOR DIELECTRIC WITH IMPROVED ELECTRICAL PROPERTIES/Senzaki; Brichko; Herring	07/17/03		PCT

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Reference No.		Title/Inventors		Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
P	71644	MSS	IN-SITU FORMATION OF MIM CAPACITORS/Sang-In Lee	60/396,734 07/19/02	Closed	
FA	71644	TW	IN-SITU FORMATION OF MIM CAPACITORS/Sang-In Lee			
FP	71644	PC	IN-SITU FORMATION OF MIM CAPACITORS/Sang-In Lee	07/17/03		Taiwan
P	71645	MSS	ATOMIC LAYER DEPOSITION FOR CAPACITOR APPLICATIONS/Sang-In Lee	07/17/03		PCT
A	71645	MSS	ATOMIC LAYER DEPOSITION FOR CAPACITOR APPLICATIONS/Sang-In Lee	60/396,745 07/19/02	Closed, combined with 71638	
P	71653	MSS	METHOD OF MAKING METAL CAPS FOR SEMICONDUCTOR DEVICES/Kaplin	Closed, combined with 71638		
A	71653	MSS	METHOD OF MAKING METAL CAPS FOR SEMICONDUCTOR DEVICES/Kaplin	60/397,031 07/18/02	Closed	
P	71720	MSS	ATOMIC LAYER DEPOSITION OF HIGH-K METAL OXIDES FOR GATE AND CAPACITOR DIELECTRICS/Sang-In Lee; S.K. Lee; Shin; Senzaki	N/A		
A	71720	MSS	ATOMIC LAYER DEPOSITION OF HIGH-K METAL OXIDES FOR GATE AND CAPACITOR DIELECTRICS/Sang-In Lee; S.K. Lee; Shin; Senzaki	60/404,372 08/18/02	Closed	
FA	71720	TW	ATOMIC LAYER DEPOSITION OF HIGH-K METAL OXIDES FOR GATE AND CAPACITOR DIELECTRICS/Sang-In Lee; S.K. Lee; Shin; Senzaki			
FP	71720	PC	ATOMIC LAYER DEPOSITION OF HIGH-K METAL OXIDES FOR GATE AND CAPACITOR DIELECTRICS/Sang-In Lee; S.K. Lee; Shin; Senzaki	08/14/03		Taiwan
P	71721	MSS	ATOMIC LAYER DEPOSITION OF METAL SILICATES FOR HIGH-K GATE AND CAPACITOR DIELECTRICS/Sang-In Lee; S.K. Lee; Shin; Senzaki	08/18/03		PCT
				60/404,371 08/18/02	Closed	

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Reference No.		Title/Inventors		Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
A	71721	MSS	ATOMIC LAYER DEPOSITION OF METAL SILICATES FOR HIGH-K GATE AND CAPACITOR DIELECTRICS/Sang-In Lee; S.K. Lee; Shin; Senzaki			
FA	71721	TW	ATOMIC LAYER DEPOSITION OF METAL SILICATES FOR HIGH-K GATE AND CAPACITOR DIELECTRICS/Sang-In Lee; S.K. Lee; Shin; Senzaki	08/14/03		Taiwan
FP	71721	PC	ATOMIC LAYER DEPOSITION OF METAL SILICATES FOR HIGH-K GATE AND CAPACITOR DIELECTRICS/Sang-In Lee; S.K. Lee; Shin; Senzaki	08/18/03		PCT
P	71722	MSS	LOW TEMPERATURE DEPOSITION OF SILICON OXIDES AND SILICON OXYNITRIDE/Sang-In Lee; S.K. Lee; Shin; Senzaki	60/404,363 08/18/02	Closed	
A	71722	MSS	LOW TEMPERATURE DEPOSITION OF SILICON OXIDES AND SILICON OXYNITRIDE/Sang-In Lee; S.K. Lee; Shin; Senzaki			
FA	71722	TW	LOW TEMPERATURE DEPOSITION OF SILICON OXIDES AND SILICON OXYNITRIDE/Sang-In Lee; S.K. Lee; Shin; Senzaki	08/14/03		Taiwan
FP	71722	PC	LOW TEMPERATURE DEPOSITION OF SILICON OXIDES AND SILICON OXYNITRIDE/Sang-In Lee; S.K. Lee; Shin; Senzaki	08/18/03		PCT
P	71730	MSS	LOW TEMPERATURE DEPOSITION OF SILICON BASED THIN FILMS BY SINGLE WAFER HOT- WALL RAPID THERMAL CHEMICAL VAPOR DEPOSITION (RTCVD)/Senzaki; Barrelli; Teasdale;	60/408,709 09/05/02	Closed	
A	71730	MSS	LOW TEMPERATURE DEPOSITION OF SILICON BASED THIN FILMS BY SINGLE WAFER HOT- WALL RAPID THERMAL CHEMICAL VAPOR DEPOSITION (RTCVD)/Senzaki; Barrelli; Teasdale;	09/05/03		
P	71730	1	LOW TEMPERATURE DEPOSITION OF SILICON BASED THIN FILMS BY SINGLE WAFER HOT- WALL RAPID THERMAL CHEMICAL VAPOR DEPOSITION (RTCVD)/Senzaki; Barrelli; Teasdale; Sensen	Closed, combined with 71730		

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Reference No.		Title/Inventors		Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
P	71731	MSS TJH	SEQUENTIAL TWO-STEP ATOMIC LAYER DEPOSITION OF COPPER SEED LAYER/Senzaki	60/419,633 10/17/02		
A	71731	MSS	SEQUENTIAL TWO-STEP ATOMIC LAYER DEPOSITION OF COPPER SEED LAYER/Senzaki			Client Ref. # D- 7006
A	71732	MSS	TWO-STEP SEQUENTIAL GROWTH OF HIGH-K GATE DIELECTRICS BY ATOMIC LAYER DEPOSITION/Senzaki			Client Ref. # D- 7005
A	71733	MSS TJH	ANNEAL PROCESS FOR SILICON NITRIDE DIELECTRIC THIN FILMS/Senzaki; Brichko			Client Ref. D-7007
A	71748	MSS WEN	THERMAL PROCESSING SYSTEM AND CONFIGURABLE VERTICAL CHAMBER/DuBois; Nann			
FA	71748	TW	THERMAL PROCESSING SYSTEM AND CONFIGURABLE VERTICAL CHAMBER/DuBois; Nann; Wildman; Qoi; Kowalski	07/10/03		Taiwan
FP	71748	PC	THERMAL PROCESSING SYSTEM AND CONFIGURABLE VERTICAL CHAMBER/DuBois; Nann; Wildman; Qoi; Kowalski	07/10/03		PCT
A	71749	MSS TJH	PEDESTAL THERMAL SHIELD/Wildman; Qoi	Closed, combined with 71748		
A	71750	MSS TJH	THERMAL PROCESSING APPARATUS AND METHOD OF BACKFILLING A CHAMBER CLEANING/Tockman			
FA	71750	TW	THERMAL PROCESSING APPARATUS AND METHOD OF BACKFILLING A CHAMBER CLEANING/Tockman	07/10/03		Taiwan
FP	71750	CT	THERMAL PROCESSING APPARATUS AND METHOD OF BACKFILLING A CHAMBER CLEANING/Tockman	07/10/03		PCT
A	71751	MSS TJH	VACUUM ASSEMBLY WITH MULTI-STAGE VALVE SEQUENCE/Qoi			

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Reference No.			Title/Inventors		Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
FA	71751	TW	MSS	VACUUM ASSEMBLY WITH MULTI-STAGE VALVE SEQUENCE/Qui	07/10/03		Taiwan
FP	71751	PC	MSS	VACUUM ASSEMBLY WITH MULTI-STAGE VALVE SEQUENCE/Qui	07/10/03		PCT
A	71752		MSS WEN	CYCLONIC COOLING SYSTEM AND METHOD/Qui; Collins			
FA	71752	TW	MSS	CYCLONIC COOLING SYSTEM AND METHOD/Qui; Collins	07/10/03		Taiwan
FP	71752	PC	MSS	CYCLONIC COOLING SYSTEM AND METHOD/Qui; Collins	07/10/03		PCT
A	71753		MSS WEN	COOLING SYSTEM AND METHOD/Qui; Collins	Closed, combined with 71752		
A	71754		MSS	FEED FORWARD TEMPERATURE CONTROLLER/Ma	Closed		
A	71755		MSS KRG	ALIGNMENT APPARATUS AND METHOD OF ALIGNING A WAFER/Ma	on hold		
A	71756		MSS	COMMUNICATION PROTOCOL AND METHOD OF IMPROVED ROBOT THROUGHPUT/Ma			
A	71757		MSS	DISTRIBUTED SINGLE WIRE NETWORKING ELEVATOR CONTROL SYSTEM AND METHOD/Ma			
FA	71757	TW	MSS	SERVOMOTOR CONTROL SYSTEM & METHOD IN A SEMICONDUCTOR MANUFACTURING ENVIRONMENT; John Ma	07/10/03		Taiwan
FP	71757	PC	MSS	SERVOMOTOR CONTROL SYSTEM & METHOD IN A SEMICONDUCTOR MANUFACTURING ENVIRONMENT; John Ma	07/10/03		PCT
A	71758		MSS KRG	LOAD PORT; Jeffery B. Kowalski			
FA	71758	TW	MSS	LOAD PORT APPARATUS; Jeffery B. Kowalski	07/15/03		Taiwan

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Reference No.			Title/Inventors		Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
FP	71758	PC	MSS	LOAD PORT APPARATUS; Jeffrey R. Kowalski	07/15/03		PCT
A	71759		MSS	THERMAL PROCESSING CHAMBER ENVIRONMENTAL CONTROL SYSTEM AND METHOD; Alan Starnier			
FA	71759	TW	MSS	CONTROL OF A GASEOUS ENVIRONMENT IN A WAFER LOADING CHAMBER; Alan Starnier	07/15/03		Taiwan
FP	71759	PC	MSS	CONTROL OF A GASEOUS ENVIRONMENT IN A WAFER LOADING CHAMBER; Alan Starnier	07/15/03		PCT
A	71763		MSS	METHOD AND SYSTEM FOR ISOTHERMAL HEATING OF WAFERS; Jeffrey Kowalski	Closed, combined with 71748		
A	71795		MSS	HEATER ELEMENT SELECTABLE FOR VARIABLE TEMPERATURE PROCESSING/Qu			
FA	71795	TW	MSS	VARIABLE HEATER ELEMENT FOR LOW TO HIGH TEMPERATURE RANGES/Qu	07/10/03		Taiwan
FP	71795	PC	MSS	VARIABLE HEATER ELEMENT FOR LOW TO HIGH TEMPERATURE RANGES/Qu	07/10/03		PCT
A	71796		MSS	T-RAIL SUPPORT/DnBois			
FA	71796	TW	MSS	METHOD & APPARATUS FOR SUPPORTING SEMICONDUCTOR WAFERS/DnBois	07/10/93		Taiwan
FP	71796	PC	MSS	METHOD & APPARATUS FOR SUPPORTING SEMICONDUCTOR WAFERS/DnBois	07/10/03		PCT
A	71797		MSS	FEED FORWARD CONTROL SYSTEM AND METHOD/Tonckman; Radhiff (This case may be related to A-71754)			
A	71798		MSS	SYSTEM ARCHITECTURE AND METHOD FOR SEMICONDUCTOR FABRICATION/Holmes; Witten			

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Reference No.		Title/Inventors	Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries
P	71824	MSS TJH REMOTE PLASMA NITRIDATION OF HIGH-K GATE DIELECTRICS/Senzaki; Bercaw; Chatham; Higuchi; Lopata	60/424,891 11/08/02		
A	71824	MSS REMOTE PLASMA NITRIDATION OF HIGH-K GATE DIELECTRICS/Senzaki; Bercaw; Chatham; Higuchi; Lopata			
A	71834	MSS TJH METHOD OF ATOMIC LAYER REMOVAL OR BLEACHING/Sang-in Lee	Closed, combined with 71606		
P	72081	MSS TRANSPORT SYSTEM HAVING SHARED LOAD- LOCK FRONT-END ASSEMBLY FOR TRANSFER OF MEDIA IN A CONTROLLED ENVIRONMENT	60/443,969 01/31/03		
P	72138	MSS ELECTRODE STRUCTURE AND METHOD OF FABRICATING AN ELECTRODE HAVING LOW TEMPERATURE OXIDE FILM; S.I. Lee, Y. Senzaki			Client Ref. No. - D-7031
P	72218	MSS METHOD OF FABRICATING MULTI-COMPONENT FILMS; Y. Senzaki, S.G. Park	60/464,458 04/21/03		Client Ref. No. - D-2419
P	72314	MSS METHOD OF FABRICATING GAS DELIVERY MANIFOLD; DeDonney, Mac	60/475,079 05/31/03		Client Ref. No. D-2493
A	72332	MSS IN-SITE CLEANING OF COPPER DETECTION CHAMBER & PARTS			
A	72333	MSS METHOD OF REDUCING CONTACT RESISTANCE OF COPPER INTERCONNECT			
A	72344	MSS BATCH FURNACE WAFER RADIAL DELTA TEMPERATURE CONTROL USING A BOTTOM AND TOP HEATER			
A	72345	MSS SEMICONDUCTOR VERTICAL FURNACE HALO RING CONCEPT; D. DuBois, C. Porter, M. Mogard			

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1059125

Reference No.			Title/Inventors		Serial No./ Filing Date	Patent No./ Issue Date	Foreign Countries

Reference Nos:
 "A" denotes US a patent/patent application/invention disclosure
 "FA" "FP" and "FF" denote a foreign patent/patent application